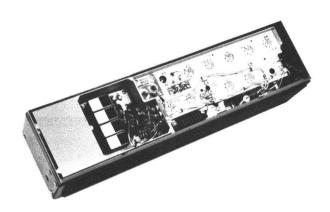


# MASTR PROGRESS LINE

470-512 MHz, RECEIVER MODELS 4ER42K10-33 & 4ER42L10-33



# **SPECIFICATIONS** \*

FCC Filing Designation

Frequency Range

Audio Output

Sensitivity

12-dB SINAD (EIA Method) 20-dB Quieting Method

Intermodulation (EIA)

Selectivity

EIA Two-Signal Method 20-dB Quieting Method

Spurious Response

First Oscillator Stability

Type ER-42-K Receivers Type ER-42-L Receivers

Modulation Acceptance

Squelch Sensitivity

Critical Squelch Standard Receiver UHS Receiver Maximum Squelch

Maximum Frequency Separation

Frequency Response

### ER-42-K&L

470 - 512 MHz

5 watts at less than 5% distortion

	Ultra-High				
Standard Receiver	Sensitivity Receiver				
0.40 μV	0.25 μV				
0.55 μV	0.30 µV				
75 40	70 10				

-85 dB (adjacent channel, 25 kHz channels) -100 dB at  $\pm 20$  kHz

-100 dB

 $\pm .0005\%$  (-30°C to +60°C) +.0002% (-30°C to +60°C)

 $\pm 7.5$  kHz

0.2  $\mu V$  0.15  $\mu V$  Greater than 20 dB quieting (less than 1.5  $\mu V)$ 

0.49

+1 and -8 dB of a standard 6-dB per octave de-emphasis curve from 300 to 3000 Hz (1000-Hz reference)

<sup>\*</sup>These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

## **TABLE OF CONTENTS**

SPECIFICATIONS	Cover
DESCRIPTION	1
CIRCUIT ANALYSIS	1
RF Amplifier Helical Resonators 1st Oscillator and Multiplier Multiplier Board 1st Mixer High IF Amplifier and Crystal Filter 2nd Oscillator, 2nd Mixer and 1st IF Amplifier 2nd Lo IF Amplifier and Limiters Discriminator Audio-Noise Amplifier Audio Amplifiers Squelch Channel Guard	1 2 2 3 3 3 3 3 3 3 3 4 4
MAINTENANCE	5
Disassembly	5 7 8
Audio Power Output and Distortion	8 8 8
Receiver Troubleshooting	9
OUTLINE DIAGRAM	10
SCHEMATIC DIAGRAM	12
PARTS LIST	11
ILLUSTRATIONS	
Figure 1 Block Diagram Figure 2 FET Nomenclature Figure 3 Removing Top Cover Figure 4 Removing Bottom Cover Figure 5 Coaxial Cable and Test Loop Figure 6 ICOM Frequency Connection Curve Figure 7 Test Setup for 20-Hz Double-Trace Sweep Alignment Figure 8 Detector Probe for Sweep Alignment	1 2 6 6 7 7 7

### ---WARNING--

No one should be permitted to handle any portion of the equipment that is supplied with high voltage; or to connect any external apparatus to the units while the units are supplied with power. KEEP AWAY FROM LIVE CIRCUITS.

### **DESCRIPTION**

General Electric MASTR Progress Line Receivers Types ER-42-K & L are double-conversion, superheterodyne FM receivers designed for operation in the 470-494 and 494-512 megahertz bands. The Type ER-42-K Receivers contain a standard oscillator with a frequency stability of ±0.0005%, while the Type ER-42-L Receivers contain an Integrated Circuit Oscillator Module (ICOM) with a frequency stability of ±0.0002%. Standard and ultra-high sensitivity (UHS) versions are available for both types.

The receivers are of single-unit construction and are completely housed in an aluminum casting for maximum shielding and rigidity. The top part of the casting contains the front end through the 1st low IF amplifier stages. The bottom portion of the casting contains the audio squelch board and the optional Channel Guard encoder-decoder board.

### **CIRCUIT ANALYSIS**

The MASTR Progress Line Receiver is completely transistorized, using silicon

transistors throughout for added reliability. Input leads to the receiver are individually filtered by the 20-pin feed-through by-pass connector J443. A regulated +10 volts is used for all receiver stages except the audio PA stage which operates from the 12-volt system supply.

Centralized metering jack J442 is provided for use with General Electric Test Set Models 4EX3A10 or 4EX8K11, for ease of alignment and servicing. The Test Set meters the oscillator, multiplier, and limiter stages as well as the discriminator, and regulated 10 volts.

### RF AMPLIFIER (A410/A411)

RF Amplifier A410/A411 is used only in ultra-high sensitivity (UHS) receivers and consists of two tuned helical resonators and an RF amplifier (Q1).

The RF amplifier uses a Field-Effect Transistor (FET) as the active device. A FET may be considered a semiconductor current path (or channel) whose resistance is varied by a voltage applied between the "gate" and "source" terminals. Lead identification for the FET is shown in Figure 2A. The FET has voltage-controlled characteristics, and may be compared to a vacuum tube in operation (see Figure 2B).

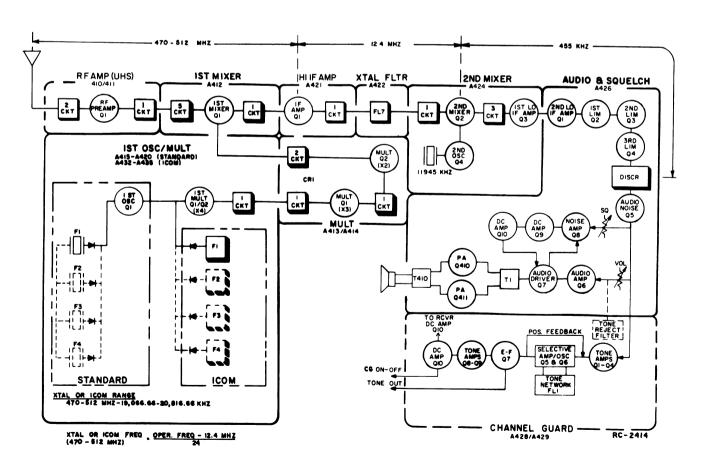


Figure 1 - Receiver Block Diagram

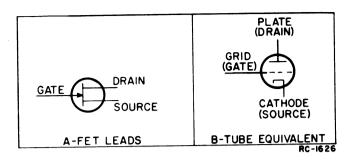


Figure 2 - FET Nomenclature

RF from the antenna is coupled through cable W444 to a tap on L410/L412. The tap is positioned to provide the proper impedance match to the antenna. RF energy is coupled to L411/L413 through an opening in the shield wall, and then to the source terminal of FET Q1.

Ql operates as a grounded-gate amplifier. This method of operation provides a low impedance input to the amplifier. The amplified output is taken from the drain terminal and coupled through a tuned circuit (C7 and L2/L3) to the input of five helical resonators.

### HELICAL RESONATORS

In receivers without the UHS option, the front end RF selectivity is provided by five tuned helical resonators (L414/L419 through L418/L423). RF cable W441 connects the RF signal from the antenna to a tap on L414/L419. The tap is positioned to provide the proper impedance match to the antenna. The output of L418/L423 is coupled through capacitor C1 to the 1st mixer assembly.

### 1ST OSCILLATOR AND MULTIPLIER

Receiver Models 4ER42K10-33 are equipped with standard Oscillator/Multiplier Boards A415-A420. Receiver Models 4ER42L10-33 are equipped with Oscillator/Multiplier Boards which use the Integrated Circuit Oscillator Module (ICOM).

# Standard Oscillator/Multiplier Board (A415-A420)

The oscillator in the standard Oscillator/Multiplier Board is a transistorized Colpitts oscillator. The oscillator crystal operates in a fundamental mode at a frequency of approximately 16 to 29 megahertz. The crystal is cut to provide temperature compensation at the high end of the termperature range and is thermistor compensated at low temperatures. This provides instant warm-up with a frequency stability of

±0.0005% without crystal ovens or warmers.

In single-frequency receivers, a jumper from H1 to H2 connects regulated +10 volts to the crystal circuit. Feedback for the oscillator is developed across C34.

In multi-frequency receivers, a diode is connected in series with the crystal and up to three additional crystal circuits can be added. The 10-volt jumper is removed, and the proper frequency is selected by switching the desired crystal circuit to +10 volts by means of a frequency selector switch on the control unit. Switching the +10 volts to the crystal circuit forward biases the diode in series with the desired cyrstal, and the crystal frequency is applied to the base of oscillator transistor Q1. The oscillator output is coupled through C32 to the base of 1st Multiplier Q2.

The 1st multiplier output is coupled through T1/T2 to Multiplier Board A413/A414. T1/T2 is tuned to four times the crystal frequency. The 1st multiplier stage is metered at J442-4 through metering network C38, CR6, R17 and R18.

# Oscillator/Multiplier Board with ICOM (A432-A435)

Oscillator/Multiplier Boards A432-A435 uses ICOM Module Model 4EG26A10. The ICOM module consists of a crystal-controlled Colpitts oscillator, a voltage regulator, and a buffer output stage. The entire module (including crystal) is enclosed in a dust-proof aluminum can, with the ICOM frequency and the receiver operating frequency printed on the top. Access to the oscillator trimmer is obtained by prying off the plastic GE decal on the top of the can.

The oscillator frequency is temperature-compensated at both ends of the temperature range to provide instant frequency compensation, with a frequency stability of  $\pm 0.0002\%$  without crystal ovens or warmers.

In single-frequency receivers, +10 volts for operating the ICOM is obtained by a jumper from H1 to H2. With the ICOM operating, diode CR1 is forward biased and the oscillator output is applied to the 1st multiplier Q1.

The 1st multiplier output is coupled through T1/T2 to multiplier board A413/A414. T1/T2 is tuned to four times the ICOM frequency. The 1st multiplier stage is metered at J442-4 through metering network C4, CR5, R5 and R6.

In multi-frequency receivers, up to three additional ICOM modules can be plugged into the board. The 10-volt jumper is removed and the proper frequency is selected by switching the desired ICOM to +10 volts by means of a frequency selector switch on the control unit.

All ICOM modules are individually compensated at the factory, and cannot be repaired in the field. Any attempt to remove the ICOM cover will void the warranty.

CAUTTON .

### MULTIPLIER BOARD (A413/A414)

Following the oscillator board are two multiplier stages. A413-Q1 operates as a tripler, and Q2 operates as a doubler. Q2 is metered at J442-1 across metering resistor R6.

The output of Q2 is coupled through two helical resonator circuits to the source terminal of the 1st mixer. The helical resonators are tuned to six times the 1st multiplier output for a total multiplication of 24 times the crystal frequency.

### 1ST MIXER (A412)

The 1st Mixer uses a Field-Effect Transistor (FET) as the active device (Fig. 2). The FET mixer has several advantages over a conventional transistor mixer, including a high input impedance and an output that is relatively free of harmonics (low in intermodulation products).

RF from the hilical resonators is applied to the gate of Ql, and injection voltage from the multiplier is applied to the source. The mixer output is taken from the drain with the output tuned to the 12.4 MHz high IF frequency.

# HI IF AMPLIFIER (A421) AND CRYSTAL FILTER (A422)

A series-resonant circuit (A412-L2 and -C3) couples the mixer output to the emitter of the high IF amplifier A421. The transistor is connected as a grounded-base amplifier which provides a low impedance for the mixer input. The amplifier output is coupled through transformer T1 to the crystal filter.

Highly-selective crystal filter A422 provides the major selectivity for the receiver. The output of the filter is coupled through impedance-matching transformer A424-T2 to the base of the 2nd mixer.

# 2ND OSCILLATOR, 2ND MIXER AND 1ST LO IF AMPLIFIER (A424)

A424-Q4 operates in a Colpitts oscillator circuit, with feedback supplied through C18. The oscillator low-side injection voltage (11,945 kHz) is applied to the base of the 2nd mixer.

The High IF signal from the filter and the injection voltage from the 2nd oscillator is applied to the base of 2nd mixer Q2. The 445-kHz mixer output is applied to three tuned low IF circuits, L, L2 and L3. These tuned circuits are required for shaping the nose of the IF waveform, and for rejecting any undesired output frequencies from the 2nd mixer.

The low IF signal is applied to the base of 1st low IF amplifier Q3. The output of Q3 is R-C coupled to the base of the 2nd low IF amplifier.

### 2ND LO IF AMPLIFIER AND LIMITERS (A426)

Additional amplification of the low IF signal going to the limiter stages is provided by 2nd low IF amplifier A426-Q1. This stage is metered at J442-2 through a metering network consisting of C19, CR3 and R25.

Following the 2nd low IF amplifier are three R-C coupled limiter stages (a426-Q2, -Q3 and -Q4). The 1st limiter is metered at J442-3 through metering network C20, CR4 and R26.

### DISCRIMINATOR (A426)

The limiter output is applied to a Foster-Seely type discriminator, where diodes CR1 and CR2 rectify the 455-kHz signal to recover the audio. The discriminator is metered at J442-10 through metering network C16 and R23.

### AUDIO - NOISE AMPLIFIER (A426)

The discriminator output is coupled through a low-pass filter (C16, C18, R21 and R22) to the base of audio-noise amplifier Q5. The filter removes any 455-kHz signal remaining in the discriminator output. Q5 operates as a emitter-follower to match the discriminator impedance to the VOLUME control, SQUELCH control, and Channel Guard input. The stage also provides power gain.

### AUDIO AMPLIFIERS (A426)

Any audio present in the incoming signal is coupled from the emitter of Q5 through the VOLUME control and a de-emphasis network to the base of audio amplifier Q6. The de-ehphasis network consists of C22, C23, R30 and R31.

Audio driver Q7 follows the audio amplifier. The audio output of Q7 is coupled through transformer T1 to provide phase inversion for the push-pull audio PA stage.

Q410 and Q411 operate as a push-pull Class AB audio PA stage. The PA output is coupled through audio transformer T410 to the loudspeaker. The yellow and white tertiary windings of T410 supply balanced feedback to the collector of Q7. The feedback winding minimizes distortion and prevents the pick-up of external electrical noise.

Base bias for the PA stage and the elimination of crossover distortion is controlled by bias adjust potentiometer R43. The potentiometer is set at the factory as shown in STEP 1 of the receiver Test Procedure.

-NOTE-

Do not adjust bias adjust potentiometer R43 unless PA transistors Q410 and Q411 have been replaced.

Audio high and low are also present at centralized metering jack J442, and can be used as shown in STEP 1 of the receiver Test Procedure. The output stage provides 5 watts at less than 5% distortion into a 3.5-ohm load at the receiver output terminals (3.2-ohms load at the Control Unit).

### SQUELCH (A426)

Noise from the audio-noise amplifier operates the squelch circuit. With no carrier present in the receiver, this noise is coupled to the base of noise amplifier Q8 through a high-pass filter which attenuates frequencies below 3 kHz. The filter consists of C30, C31 and R45, as well as C34 and L3 in the collector circuit of Q8. The gain of Q8 is determined by the Squelch control, which varies the bias on the base of Q8. Thermistor RT2 keeps the critical squelch constant over wide variations in temperature.

The output of noise amplifier Q8 is rectified by diodes CR5 and CR6, and filtered by C36 and C37 to produce a negative DC voltage. This DC voltage is applied to the base of DC amplifier Q9, turning it off. When turned off, the collector voltage of Q9 rises to approximately 8 volts, turning on DC amplifier Q10. When conducting, the collector voltage of Q10 drops to almost ground potential, which removes the base bias to audio amplifier Q6 and audio driver Q7, turning them off.

When the receiver is quieted by a signal (unsquelched), the noise in the receiver is reduced, turning DC amplifier Q9 on and DC amplifier Q10 off. This allows the audio stages to conduct so that sound is heard in the speaker.

Resistor R53 connects from the emitter of audio driver Q7 to the emitter of noise amplifier Q8, providing a hysteresis loop in the squelch circuit. When a weak signal opens the squelch circuit. When a weak signal opens the squelch, the signal level may be reduced by 4 to 6 dB without the squelch closing. This limits squelch "flutter" or "picket-fence" operation.

With audio driver Q7 conducting, a positive voltage through R53 helps to reduce the gain of noise amplifier Q8. This positive feedback provides a quick, positive switching action in the squelch circuit. When the receiver squelches, audio driver Q7 turns off and its emitter potential drops to zero. This reduces the DC feedback through R53 to the emitter of noise amplifier Q8. Reducing the feedback causes Q8 to conduct harder, turning the audio stages off quickly.

Keying the transmitter removes the  $\pm 10$  volts from J19, turning off DC amplifier Q9 and turning on Q10 to mute the receiver.

### CHANNEL GUARD (A428/A429)

Channel Guard Board Model 4EK16A10 is a fully transistorized encoder-decoder for use in the MASTR Professional Series mobile and station combinations. The tone frequencies are controlled by plug-in tone networks that are made with precision components for excellent stability and reliability. The tone frequencies range from 71.9 to 203.5 Hz.

### Encoder (A428)

Keying the transmitter removes the receiver mute +10 volts, and forward biases feedback control diode CR5, causing it to conduct. When conducting, the diode shunts R39 which reduces the impedance of the positive feedback loop (R39, R35 and C19). This provides the necessary gain to the base of Q5 to permit oscillation.

The encoder tone is provided by selective amp-oscillator transistors Q5 and Q6 which oscillate at a frequency determined by the tone network. Negative feedback applied through the tone network to the base of Q5 prevents any gain in the stage except at the desired encode frequency.

Starting network R45, C21, C22 and CR6 provide an extremely fast starting time for the encoder tone. Keying the transmitter removes the receiver mute +10 volts, causing a pulse to be applied to the base of Q6 to quickly start the oscillator. Thermistorresistor combination R32 and RT1 provides termperature compensation for the oscillator output. Limiter diodes CR3 and CR4 keep the tone amplitude constant.

Emitter-follower Q7 follows the oscillator circuit. The encoder tone is taken from the emitter of Q7 and applied to an active low-pass filter (G101) on the transmitter.

### Decoder (A428)

The decoder function is designed to eliminate all calls that are not tone coded for the Channel Guard frequency. As long as the CHANNEL GUARD-OFF switch on the control unit is left in the CHANNEL GUARD position, all signals are locked out except those from transmitters that are continuously tone coded for positive identification by the receiver.

Placing the CHANNEL GUARD-OFF switch in the OFF position instantly disables the Channel Guard operation so that all calls on the channel can be heard. When the hookswitch option is used, lifting the microphone from its hanger disables the Channel Guard Circuit.

Audio, tone and noise are taken from the emitter of the receiver audio-noise amplifier A426-Q5 and is fed through A428-Jl to four tone amplifier and bandpass filter circuits. The filters remove the audio and high-frequency noise from the signal, and the tone amplifiers provide sufficient gain to insure clipping by limiter diodes CR1 and CR2. The clipping action eliminates variation in the squelch performance due to changes in tone deviation. The signal is then applied to selective amplifiers Q5 and Q6 which amplify only the tone determined by the tone network.

The output of the selective amplifier is applied through emitter-follower Q7 to the high gain, broad-band tone amplifiers Q8 and Q9. The output of Q9 is rectified by detector diodes CR7 and CR8, and the resulting negative DC voltage controls the squelch gate. Q8 is normally biased for low gain. Then the tone is detected by CR7 and CR8, feedback is provided through R54 to quickly change the bias on Q8 for full gain. This ensures a more positive "unsquelching" action.

Squelch gate diode CR9 is normally forward biased by a positive DC voltage (approximately 1.5 volts) fed through R58. The forward bias causes CR9 to conduct, feeding a DC voltage to the base of DC amplifier A426-Q10 in the receiver. This removes the bias on the receiver audio stages and holds them off.

When the proper tone is applied to the decoder, the negative DC voltage from the detector diodes back-biases squelch gate diode CR9 and cuts off the positive bias to the receiver DC amplifier A426-QlO. However, the receiver noise squelch circuit continues to operate until a carrier quiets the receiver.

Placing the CHANNEL GUARD - OFF switch in the OFF position (or removing the microphone from its hookswitch) removes the ground to the base of the decoder DC switch (Q10), causing it to conduct. This back-biases squelch control diode CR9 and cuts off the positive bias to the receiver DC amplifier (A426-Q10). The receiver noise squelch circuit continues to operate until a carrier quiets the receiver.

A tone rejection filter connected in parallel with A426-J2 (in the receiver bypasses any incoming tone to ground. This attenuates the tone level reaching the receiver audio circuits. The filter is composed of C26, C27, C28, C29, L1 and R59.

An optional tone reject filter (A429) that is identical to the filter dexcribed above is available for use in two-way radios with transmitter Channel Guard only.

### **MAINTENANCE**

### DISASSEMBLY

To service the receiver from the top-

- Pull locking handle down and pull radio about one inch out of mounting frame. (see Fig. 3).
- 2. Pry up cover at rear of receiver.
- 3. Slide cover back and lift off.

To service the receiver from the bottom-

- Pull locking handle down. Pull radio out of mounting frame. (see Figure 4).
- Remove screws in bottom cover. Pry up cover at back of receiver.
- 3. Slide cover back and lift off.

To remove the receiver from the system frame-

- Loosen the two Phillips-head retaining screws in front casting (see Figure 3), and pull casting away from system frame.
- Remove the four screws in the back cover.
- Remove the two screws holding the receiver at each end of the system frame.
- 4. Disconnect the antenna jack and the 20pin connector from the front of the receiver, and slide the unit out of the system frame.

LBI-4434 MAINTENANCE

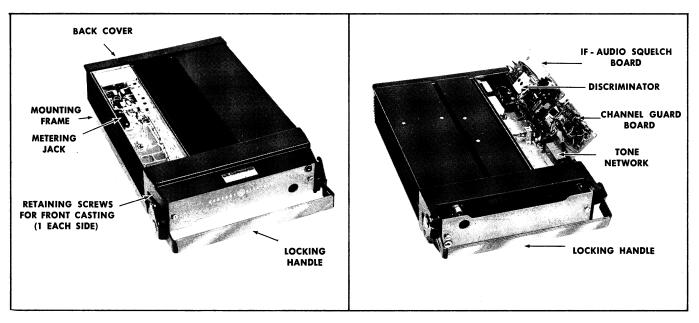


Figure 3 - Removing Top Cover

Figure 4 - Removing Bottom Cover

## COMPLETE RECEIVER ALIGNMENT

### EQUIPMENT REQUIRED

- 1. GE Test Set Models 4EX3AlO, 4EX8Kll, station test meter panel, or 20,000 ohms-per-volt multimeter.
- 2. A 450 to 460 kHz source (GE Test Set Model 4EX7A10), and 470-512 MHz signal source. Connect a one-inch piece of insulated wire no larger than .065 inch to generator output probe.

### PRELIMINARY CHECKS AND ADJUSTMENTS

- 1. Connect Test Set to receiver centralized metering jack J442, and set meter sensitivity switch to the TEST 1 or 1-volt position.
- For a large change in frequency or a badly mis-aligned receiver, set crystal trimmer C9 on 1st OSC/MULT board (ER-42-K only) to mid-capacity.
   In multi-frequency receivers, set C10, C11 or C12 to mid-capacity as required.
- 3. In multi-frequency receivers where the maximum frequency spacing is less than 500 kHz, align the unit on channel Fl. If the frequency spacing is greater than 500 kHz, align the receiver on the center frequency.
- 4. With Test Set in position J, check for regulated +10 volts. If using Multimeter, measure from C425 to C426.
- 5. If using Multimeter, connect the positive lead to J442-16 (ground).
- 6. Disable the Channel Guard.

### ALIGNMENT PROCEDURE

STEP	METERING GE Test Set or Meter Panel	Multimeter	TUNING CONTROL	METER READING	PROCEDURE
				DISCRIMINATOR	
1.	A (DISC)	Pin 10	L1 and L2 (on IF-AUDIO SQUELCH board)	Zero	Remove three screws and swing open the IF-AUDIO & SQUELCH board. Adjust L1 (disc primary) 1/2 turn counterclockwise from the bottom of coil. Next, apply a 455-kHz signal to J2 and J4 and adjust L2 (disc secondary) for zero meter reading.
2.	A (DISC)	Pin 10		See Pro- cedure	Alternately apply a 450-kHz and 460-kHz signal and check for readings of at least 0.3 volt, but not more than 0.5 volt on GE Test Set. Both readings must be within .05 volt. Do not attempt to balance reading any closer than 0.05 volt.
			OSCILL	ATOR AND MULTIP	PLIERS
3.	D (MULT-1)	Pin 4	L5 (1st OSC/MULT) and L1 (2nd MULT)	See Pro- cedure	Tune L5 for maximum meter reading. Then tune L1 for minimum meter reading.
4.	G (MULT-1)	Pin 4	L5 (1st OSC/MULT) and L1 and L2 (2nd MULT)	Maximum	Tune L5, L1 and L2 for maximum meter reading. If two peaks occur while tuning L1 and L2, use the peak with the slug nearest the top of the coil.
5.	G (MULT-2)	Pin 4	C423	See Pro- cedure	Adjust C423 for a small dip in meter reading.
6.	A (DISC)	Pin 10		Zero	Apply an on-frequency signal into Hole 4ll. Adjust the signal generator for discriminator zero.
7.	B (2nd IF AMP)	Pin 2	C423 and C424	Maximum	Apply an on-frequency signal as above. Tune C423 and C424 for maximum meter reading, keeping signal below saturation.
				RF SELECTIVITY	
8.	B (2nd IF AMP)	Pin 2	L3 (1st Mixer)	Maximum	Apply an on-frequency signal in Hole 411 and tune L3 for maximum meter reading. If two peaks occur, use the peak with the slug nearest the bottom of the coil.
9.	B (2nd IF AMP)	Pin 2	C415 thru C418	Maximum	Apply an on-frequency signal in the Hole shown below, keeping the signal below saturation. Tune C415 thru C418 for maximum meter reading as shown below:
					Insert Generator Probe In:
					1. Hole 411 C418 thru C417
					2. Hole 410 C415, C416 thru C417
10.	(2nd IF AMP)	Pin 2	C414 thru C418, L3 (on 1st Mixer) and C410, C411 and C7 (on UHS receivers)	See Pro- cedure	Apply an on-frequency signal to the receiver antenna jack. Tune C410, C411 and C7 on UHS receivers for maximum meter reading. On all receivers, tune C414 for maximum meter reading, and tune C415 thru C418 and L3 for maximum quieting.

The 2nd mixer, and high IF circuits have been aligned at the factory and will normally require no further adjustment. If adjustment is necessary use the procedure outlined in STEPS 11, 12 and 13.

Refer to DATAFILE BULLETIN 1000-6 IF Alignment of Two-Way Radio FM Receivers for helpful suggestions on how to determine

11.	В	Pin 2	L3, L2, L1, T2 (2nd Mixer)	Maximum	Apply on-frequency, unmodulated signal and tune L3, L2, L1, T2 (2nd
	(2nd IF AMP)		and Tl (Hi IF AMP)		mixer) and TI (Hi IF AMP) for maximum meter reading, keeping signal below saturation.
12.			L3, L2, L1, T2 (2nd Mixer) and T1 (Hi IF AMP)		Connect scope, signal generator, and detector as shown in Figure 7. Set signal generator level for $30-50~\mu v$ and modulate with 10 kHz at 20 Hz. With detector at the collector of Q3 (2nd mixer board output), tune for double trace as shown on scope pattern.
13.	A (DISC)	Pin 10		See Pro- cedure	Check to see that discriminator idling voltage in within $\pm$ .06 volt of zero with no signal applied. Check to see that modulation acceptance bandwidth is between $\pm$ 7.5 and 9 kHz.
		1		FREQUENCY	ADJUSTMENT
14.	Refer to the app	ropriate a	djustment procedure for the ICOM		

## FRONT END ALIGNMENT

### EQUIPMENT REQUIRED

- 1. GE Test Set Model 4EX3A10, 4EX8K11 station test meter panel or 20,000 ohms-per-volt multimeter
- 2. A 470-512 MHz signal source. Connect a one-inch piece of insulated wire no larger than 0.065 inch to generator output probe.

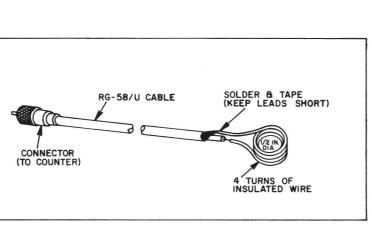
### PRELIMINARY CHECKS AND ADJUSTMENTS

- 1. Connect Test Set to receiver centralized metering jack J442 and set meter sensitivity switch to the TEST 1 (or 1-volt position on 4EX8K11).
- With Test Set in position J, check for regulated +10 volts. If using Multi-meter, measure from C425 to C426.
- 3. If using Multimeter, connect the positive lead to J442-16 (ground).
- 4. Disable the Channel Guard.

METERING POSITION

### ALIGNMENT PROCEDURE

	METERING PO	SITION			
TEP	GE Test Set or Meter Pane	Multimeter - at J442	TUNING CONTROL	METER READING	PROCEDURE
		OSCILLAT	OR AND MULTIPLIERS		
	D (MULT-1)	Pin 4	L5 (1st OSC/MULT) and L1 (2nd MULT)	See Pro- cedure	Tune L5 for max- imum meter read- ing. Then tune L1 for minimum meter reading.
•	G (MULT-2)	Pin 4	L5 (1st OSC/MULT) and L1 and L2 (2nd MULT)	Maximum	Tune L5, L1 and L2 for maximum meter reading. If two peaks occur while tuning L1 and L2, use the peak with the slug nearest the top of the coil.
•	G (MULT-2)	Pin 4	C423	See Pro- cedure	Adjust C423 for a small dip in meter reading.
•	A (DISC)	Pin 10		Zero	Apply on on-frequency signal into Hole 411. Adjust the signal generator for discriminator zero.
	B (2nd IF AMP)	Pin 2	C423 and C424	Maximum	Apply an on-frequency signal as above. Tune C423 and C424 for maximum meter reading, keeping signal below saturation.
		R	F SELECTIVITY		
-	B (2nd.IF AMP)	Pin 2	L3, C415-C418	Maximum	Apply an on-frequency signal in Hole 411 and tune L3 and C415 thru C418 for maximum meter reading, keeping the signal below saturation. If two peaks occur when tuning L3, use the peak with the slug nearest the bottom of the coil.
•	B (2nd 1F AMP)	Pin 2	C414 thru C418, L3 (on 1st Mixer) and C410, C411 and C7 (on UHS receivers)	See Pro- cedure	Apply on on-frequency signal to the receiver antenna jack. Tune C410, C411 and C7 on UHS receivers for maximum meter reading. On all receivers, tune C414 for maximum meter reading, and then tune C415 thru C418 and L3 for maximum quieting.
_		FREQ	UENCY ADJUSTMENT		
	Refer to the app Oscillator.	propriate ad	justment procedure f	or the ICOM	or Standard
-					



RC-1600 Figure 5 - Coaxial Cable and Test Loop

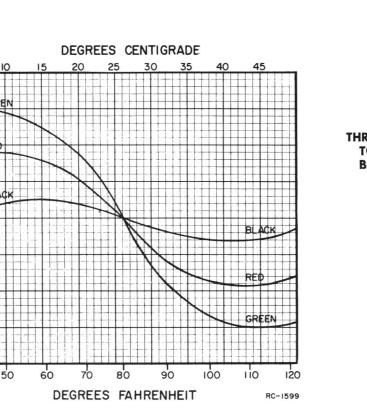
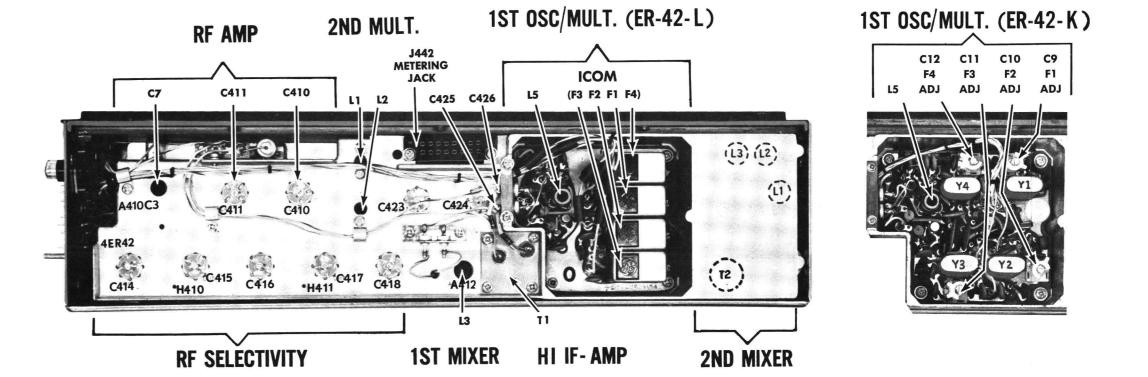


Figure 6 - ICOM Correction Curves

-1.5







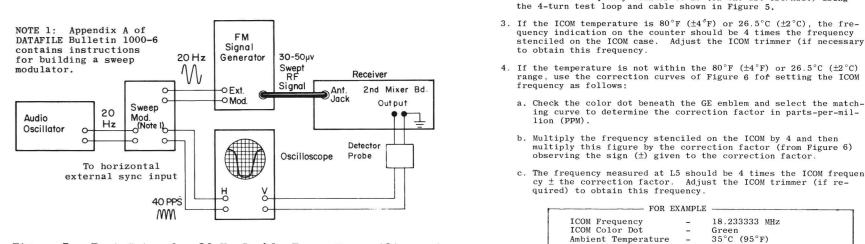


Figure 7 - Test Setup for 20-Hz Double-Trace Sweep Alignment

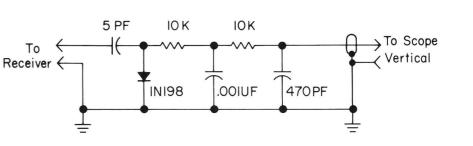


Figure 8 - Detector Probe for Sweep Alignment

# FREQUENCY ADJUSTMENT LBI-4434

### STANDARD OSCILLATOR

METERING MEXSA10	POSITION Multi- meter	TUNING CONTROL	METER READING	PROCEDURE
A (Disc)	-at J442 Pin 10	C9 (on 1st OSC/ MULT) C10, C11 and C12 for multi- frequency	Zero	Apply an on-frequency signal to the antenna jack. Tune C9 for zero discriminator reading. In multi-frequency units, tune C10, C11 or C12 as required.

## ICOM MODULE

Due to the high stability of the ICOM module, it is not recommended that zero discriminator be used as the indication for setting the oscillator frequency. Instead, measure the ICOM frequency as described in

### EQUIPMENT REQUIRED:

- 1. Frequency Counter capable of measuring the 70-80 MHz frequency range. (The counter should have an accuracy of 0.4 part-per
- 2. Coaxial cable with test loop as described in Figure 5.
- 3. Mercury thermometer.

72.933332 MHz

- .000084 MHz 72.933248 MHz

## PROCEDURE:

- 1. Check the ICOM temperature by taping the mercury thermometer to the side of the ICOM.
- 2. Connect the frequency counter to L5 (on the 1st Osc/Mult) using the 4-turn test loop and cable shown in Figure 5.
- quency indication on the counter should be 4 times the frequency stenciled on the ICOM case. Adjust the ICOM trimmer (if necessary) 4. If the temperature is not within the  $80\,^{\circ}F$  ( $\pm4\,^{\circ}F$ ) or  $26.5\,^{\circ}C$  ( $\pm2\,^{\circ}C$ )
- range, use the correction curves of Figure 6 for setting the ICOM frequency as follows:
- a. Check the color dot beneath the GE emblem and select the matching curve to determine the correction factor in parts-per-million (PPM). b. Multiply the frequency stenciled on the ICOM by 4 and then multiply this figure by the correction factor (from Figure 6)
- observing the sign (±) given to the correction factor.
- c. The frequency measured at L5 should be 4 times the ICOM frequency  $\pm$  the correction factor. Adjust the ICOM trimmer (if required) to obtain this frequency. - FOR EXAMPLE -

ICOM Frequency ICOM Color Dot 18.233333 MHz Green 35°C (95°F) Ambient Temperature -- -1.15 PPM (From Figure 6) Multiply ICOM Frequency by 4; (18.233333 MHz x 4 = 72.933332 MHz) Multiply preceding figure by correction factor; (72.933 MHz x -1.15 PPM = -83.87 hertz (or -84 hertz Set the frequency measured at L5 for 72.933248 MHz;

# ALIGNMENT PROCEDURE

470—512 MHz MASTR RECEIVER MODELS 4ER42K10-33 & 4ER42L10-33

Issue 1

LBI-4434

# **TEST PROCEDURES**

These Test Procedures are designed to help you to service a receiver that is operating---but not properly. The problems encountered could be low power, poor sensitivity, distortion, limiter not operating properly, and low gain. By following the sequence of test steps starting with Step 1, aligned to the proper operating frequency. the defect can be quickly localized. Once

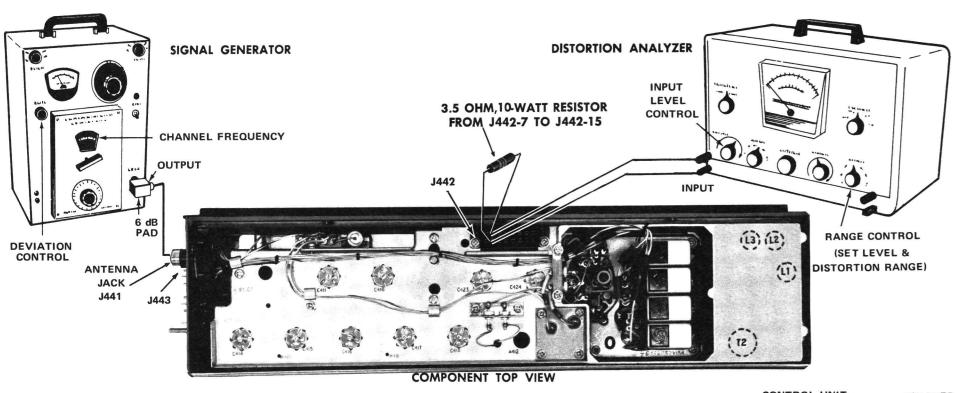
the defective stage is pin-pointed, refer to the "Service Check" listed to correct the problem. Additional corrective measures are included in the Troubleshooting Procedure. Before starting with the Receiver Test Procedures, be sure the receiver is tuned and

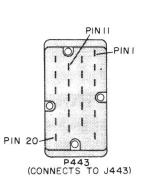
## TEST EQUIPMENT REQUIRED

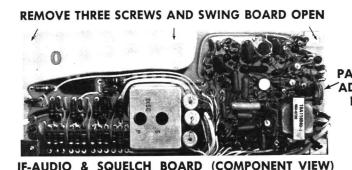
- Distortion Analyzer similar to: Heath IM-12
- Signal Generator similar to: Measurements M-560
- 6-dB attenuation pad, and 3.5-ohm, 10-watt resistor

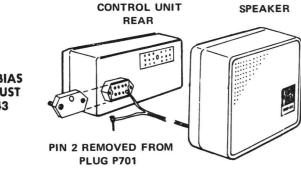
# PRELIMINARY ADJUSTMENTS

- 1. Connect the test equipment to the receiver as shown for all steps of the receiver Test Procedure.
- 2. Turn the SQUELCH control fully clockwise for all steps of the Test Procedure.
- 3. Turn on all of the equipment and let it warm up for 20 minutes.









# STEP 1

# **AUDIO POWER OUTPUT** AND DISTORTION

## TEST PROCEDURE

Measure Audio Power Output as follows:

- A. Apply a 1,000-microvolt, on-frequency test signal modulated by 1,000 hertz with ±3.3 kHz deviation to antenna jack J441.
- With Five-Watt Speaker:

Disconnect speaker lead pin from J701-2 (on rear of Control Unit).

Connect a 3.5-ohm load resistor from J442-15 to J442-7. Connect the Distortion Analyzer input across the resistor as shown.

## With Handset:

Lift the handset off of the hookswitch. Connect the Distortion Analyzer input from J442-15 to J442-7.

- Adjust the VOLUME control for five-watt output (4.18 VRMS using the Distortion Analyzer as a VTVM).
- Make distortion measurements according to manufacturer's instructions. Reading should be less than 5%. If the receiver sensitivity is to be measured, leave all controls and equipment as they are.

## SERVICE CHECK

If the distortion is more than 5%, or maximum audio output is less than five watts, make the following checks:

- Battery and regulator voltage---low voltage will cause distortion. (Refer to Receiver Schematic Diagram for voltages.)
- P.A. Bias Adjust (R43) -- Turn the SQUELCH control fully counterclockwise.

Then connect a milliammeter in series with the +12 volt lead at P443-11. With no signal in, adjust R43 for a reading of approximately 20 milliamps. This adjustment should not be necessary unless an output transistor has been rereplaced.

- G. Audio Gain (Refer to Receiver Troubleshooting Procedure).
- H. Discriminator Alignment (Refer to Receiver Alignment on reverse side of page).

# STEP 2 **USABLE SENSITIVITY** (12-dB SINAD)

If STEP 1 checks out properly, measure the receiver sensitivity as follows:

- A. Apply a 1000-microvolt, on-frequency signal modulated by 1000 Hz with 3.3-kHz deviation to J441.
- B. Place the RANGE switch on the Distortion Analyzer in the 200 to 2000-Hz distortion range position (1000-Hz filter in the circuit). Tune the filter for minimum reading or null on the lowest possible scale (100%, 30%, etc.)
- C. Place the RANGE switch to the SET LEVEL position (filter out of the circuit) and adjust the input LEVEL control for a +2 dB reading on a mid range (30%).
- While reducing the signal generator output, switch the RANGE control from SET LEVEL to the distortion range until a 12-dB difference (+2 dB to -10 dB) is obtained between the SET LEVEL and distortion range positions (filter out and filter in).
- E. The 12-dB difference (Signal plus Noise and Distortion to noise plus distortion ratio) is the "usable" sensitivity level. The sensitivity should be less than rated 12 dB SINAD specification with an audio output of at least 2.5 watts (2.9 volts RMS across the 3.5-ohm receiver load using the Distortion Analyzer as a VTVM).

F. Leave all controls as they are and all equipment connected if the Modulation Acceptance Bandwidth test is to be per-

### SERVICE CHECK

If the sensitivity level is more than rated 12 dB SINAD, check the alignment of the RF stages as directed in the Alignment Procedure, and make the gain measurements as shown on the Troubleshooting Procedure.

# STEP 3 MODULATION ACCEPTANCE **BANDWITH (IF BANDWITH)**

If STEPS 1 and 2 check out properly. measure the bandwidth as follows:

- A. Set the Signal Generator output for twice the microvolt reading obtained in the 12-dB SINAD measurement.
- Set the RANGE control on the Distortion Analyzer in the SET LEVEL position (1000-Hz filter out of the circuit), and adjust the input LEVEL control for a +2 dB reading on the 30% range.
- C. While increasing the deviation of the Signal Generator, switch the RANGE control from SET LEVEL to distortion range until a 12-dB difference is obtained between the SET LEVEL and distortion range readings (from +2 dB to -10 dB).
- The deviation control reading for the 12-dB difference is the Modulation Acceptance Bandwidth of the receiver. If should be more than ±7.5 kHz (but less that ±9.5 kHz).

## SERVICE CHECK

If the Modulation Acceptance Bandwidth test does not indicate the proper width, make gain measurements as shown on the Receiver Troubleshooting Procedure.

# STEP I-QUICKCHECKS

## TEST SET CHECKS

These checks are typical voltage readings measured with GE Test Set Model 4EX3AlO in the Test 1 position, or Model 4EX8KlO or 11 in the 1-volt position.

Metering Position	Reading with No Signal in	Reading with l μν unmodulated input
A Disc idling	Less than ±.05 VDC	
B 2nd IF	.05 VDC	0.2 VDC
C lst Lim	0.6 VDC	0.8 VDC
D Mult 1	1.0 VDC	
G Mult 2	0.3 VDC	
J Regulated +10 Volts	10 VDC	

## **SYMPTOM CHECKS**

SYMPTOM	PROCEDURE
NO SUPPLY VOLTAGE	<ul> <li>Check power connections and continuity of supply leads, and check fuse in power supply. If fuse is blown, check receiver for short circuits.</li> </ul>
NO REGULATED 10-VOLTS	• Check the 12-volt supply. Then check regulator circuit (See Troubleshooting Procedure for Power Supply).
LOW 1ST LIM READING	<ul> <li>Check supply voltages and then check oscillator reading at J442-4 &amp; 5 as shown in STEP 2A.</li> </ul>
	<ul> <li>Make SIMPLIFIED VTVM GAIN CHECKS from 2nd Mixer through 1st Limiter stages as shown in STEP 2A.</li> </ul>
LOW OSCILLATOR/MULTI- PLIER READINGS	• Check alignment of Oscillator (Refer to Front End Alignment Procedure).
	• Check voltage readings of 1st Oscillator/Multiplier Q1/Q2.
	• Check crystal Yl.
LOW RECEIVER SENSITIVITY	• Check Front End Alignment (Refer to Receiver Alignment Procedure).
	Check antenna connections, cable and relay.
	• Check 1st and 2nd Oscillator injection voltage.
	• Check voltage readings of RF Amp, 1st Mixer and HI IF Amp.
	Make SIMPLIFIED GAIN CHECKS (STEP 2A).
LOW AUDIO	• Check Audio PA (Q410 & Q411) voltage readings on schematic diagram.
	• Make simplified gain and waveform checks of audio and squelch stages (Steps 2A and 2B).
	• Make unsquelched voltage readings in Audio section (Refer to Receiver Schematic Diagram).
	• Check voltage readings on Channel Guard board.
HIGH DISTORTION AT LOW AUDIO LEVELS (50 MW)	Set PA bias adjust R43 as specified under Service checks in STEP 1 of TEST PROCEDURES.
IMPROPER SQUELCH OPERATION	• Check voltage readings of Squelch circuit (Refer to Receiver Schematic Diagram).
	<ul> <li>Make gain and waveform checks of audio and squelch stages (Steps 2A and 2B).</li> </ul>
DISCRIMINATOR IDLING TOO FAR OFF ZERO	• See if discriminator zero is in center of IF bandpass.

# STEP 3-VOLTAGE RATIO READINGS ->

### EQUIPMENT REQUIRED:

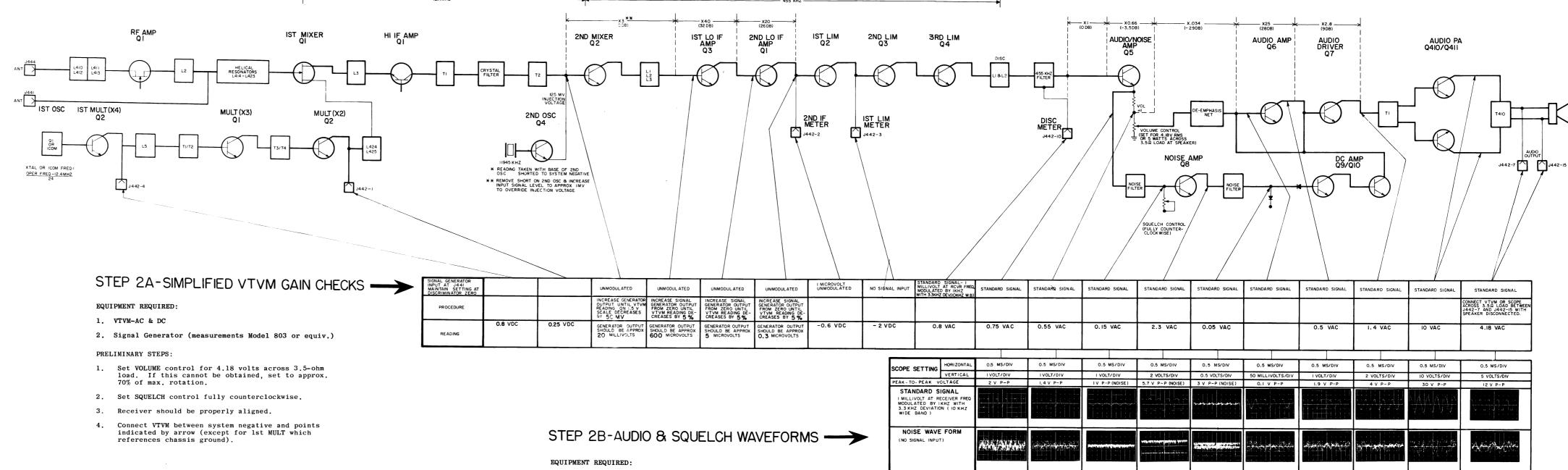
- RF Voltmeter (Similiar to Boonton Model 91-CA or Millivac Type MV-18 C).
- Signal on receiver frequency (below saturation). Correct frequency can be determined by zeroing the discriminator. Use 1,000 Hertz signal with 3.3 kHz deviation for audio stage.

### PROCEDURE

- 1. Apply probes to input of stage and system negative (-10 VDC). Take voltage reading (E $_1$ ).
- 2. Move probes to input of following stage and system negative. Take reading (E $_2$ ).
- 3. Convert readings by means of the following for-

Volatge Ratio =  $\frac{E_2}{E_1}$ 

Check results with typical voltage ratios shown on diagram.



- Oscilloscope.
- 2. Signal Generator (measurements Model 803 or equivalent).

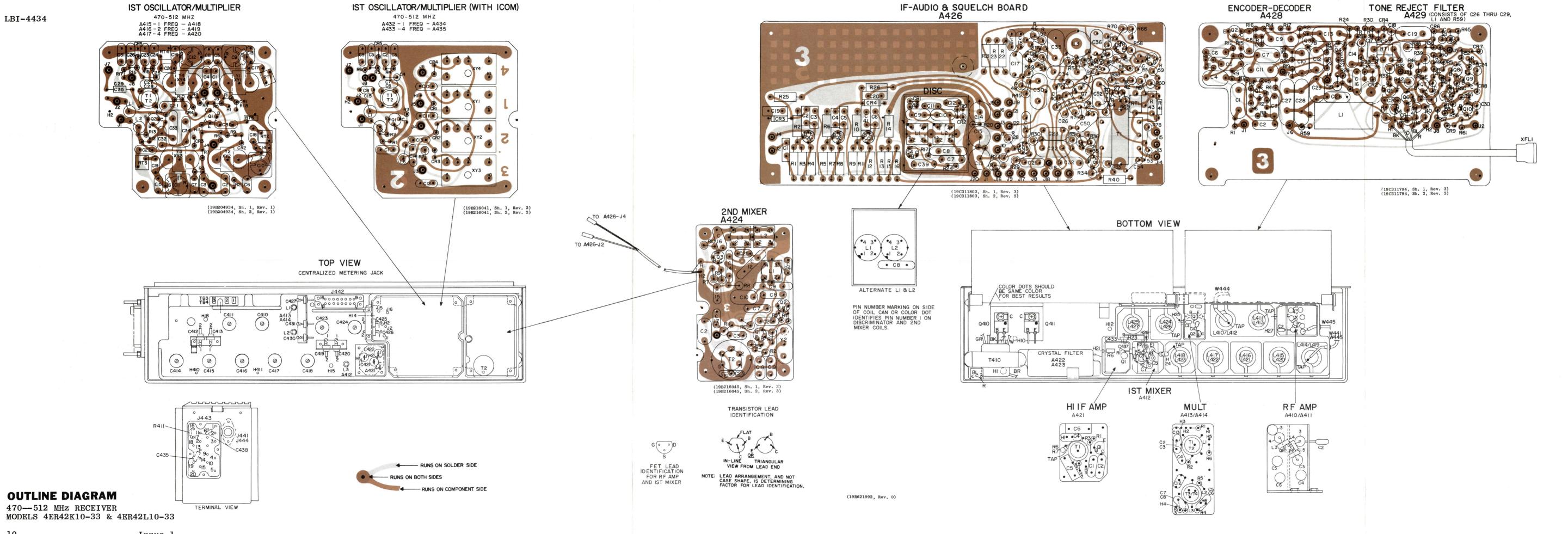
### PRELIMINARY STEPS:

- Set VOLUME control for 4.18 volts across 3.5-ohm load. If this cannot be obtained, set to approx. 70% of max. rotation.
- 2. Set SQUELCH control fully counterclockwise.
- 3. Receiver should be properly aligned.
- Connect oscilloscope between system negative and points indicated by arrow.

# TROUBLESHOOTING PROCEDURE

470—512 MHZ RECEIVER MODELS 4ER42K10-33 & 4ER42L10-33

Issue 1



LBI-4434

PARTS LIST	
LBI-4433	
470-512 MHz RECEIVERS 4ER42K10-33, 4ER42L10-33	

			R1
SYMBOL	GE PART NO.	DESCRIPTION	R2 and R3
A410 and A411		RF AMPLIFIER 19C317950G1	A413 and A414
Cl and C2	5496218P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.	C1
СЗ	5493392P5	Ceramic, feed-thru: 220 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FASC.	C2 C3
C4 thru C6	5493392P107	Ceramic, stand-off: 1000 pf +100%-0%, 500 VDCW; sim to Allen-Bradley Type SS5D.	C4
			C5
L1 and L2	19B209420P1	Coil, RF: 0.10 µh ±5%, 0.08 ohms DC res max; sim to Jeffers 4416-1J.	C6 C7
L3 thru	19A116632P1	Torridal core.	C8
L5	İ		
Q1	19A116154P1	N Channel, field effect.	C10
4-	19411010441	A Channel, field effect.	C11
		RESISTORS	C12
R1 and R2	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	and C13
			C14
A412		FIRST MIXER ASSEMBLY 19C311974G1	C15
C1	5496218P312	Ceramic disc: 18 pf ±10%, 500 VDCW, temp coef -150 PPM.	Ll
C2		(Part of L3).	L2
C3	5496218P249	Ceramic disc: 27 pf ±5%, 500 VDCW, temp coef -80 PPM.	L3
C4	19B209243P1	Polyester: 0.01 µf ±20%, 50 VDCW.	
C5	5493392P107	Ceramic, stand-off: 1000 pf +100%-0%, 500 VDCW; sim to Allen-Bradley Type SS5D.	Q1
C6	19B209243P1	Polyester: 0.01 µf ±20%, 50 VDCW.	Q2
C7	5493392P7	Ceramic, feed-thru: 1000 pf +100%-0%, 500 VDCW; sim to Allen Bradley Type FASC.	
C8		(Part of L3).	R1
			R2
El and	19B209055P8	Terminal, feed-thru.	R3 R4
E2			R5
Ll	19A127430G1	INDUCTORS	R6
L2	19A127430G1	Choke. (Part of L3).	R7
L3	19B216440G1	Coil assembly, includes:	
C2	5496218P249	Capacitor, ceramic disc: 27 pf ±5%, 500 VDCW, temp coef -80 PPM.	т1
С8	19A116114P12	Capacitor, ceramic: 3.3 pf ±5%, 100 VDCW; temp coef 0 PPM.	and T2
L2	19B209420P113	Coil, RF: 1 µh ±10%, 0.74 ohms DC res max; sim to Jeffers 4426-6.	C2
	5491798P8	Tuning slug.	
			C3

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
		TRANSISTORS			
Q1	19A116154P1	N Channel, field effect.	1		INDUCTORS
			L1		(Part of Tl and T2).
		RESISTORS	1	5491798P7	Tuning slug.
Rl	3R152P302J	Composition: 3000 ohms ±5%, 1/4 w.	T3 and		COIL ASSEMBLY T3 19B219099G1
R2 and	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	T4		T4 19B219099G2
R3					
A413 and		MULTIPLIER BOARD ASSEMBLY A413 19B219100G1	C5	5496218P236	Ceramic disc: 5.0 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.
A414		A414 19B219100G2	C6	5496218P235	Ceramic disc: 4.0 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM.
		CAPACITORS	C7	5496218P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp
C1	19A116655P12	Ceramic disc: 330 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	and C8		coef -80 PPM.
C2		(Part of T1).			
C3		(Part of T2).	1		INDUCTORS
C4	19A116720P149	Ceramic disc: 220 pf ±10%, 500 VDCW, temp coef	L2		(Part of T3 and T4).
		-3300 PPM.	1	5493185P5	Tuning slug.
C5	1	(Part of T3).	A415		FIRST OSCILLATOR ASSEMBLY
C6	1	(Part of T4).	thru A420		A415 19C317606G1 A416 19C317606G2
C7		(Part of T3).			A417 19C317606G3 A418 19C317606G4
C8		(Part of T4).	1		A419 19C317606G5 A420 19C317606G6
C9	19A116655P13	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	1		
C10	19A116720P149	Ceramic disc: 220 pf ±10%, 500 VDCW, temp coef	Cl	19A116655P20	Commission and the commission of the commission
C11	5496218P243	-3300 PPM.  Ceramic disc: 13 pf ±5%, 500 VDCW, temp coef -80 PPM.	thru C4	194110033920	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
C12 and C13	19A116655P13	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	C5 thru C8	19A116656P33J7	Ceramic disc: 33 pf ±5%, 500 VDCW, temp coef -750 PPM.
C14	5496218P544	Ceramic disc: 15 pf ±5%, 500 VDCW, temp coef -330 PPM.	C9 thru C12	5491271P106	Variable, subminiature: approx 2.1-12.7 pf, 750 v peak; sim to EF Johnson 189.
C15	5494481P7	Ceramic disc: 470 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	Cl3 thru Cl6	19A116656P9G0	Ceramic disc: 9 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
Ll		INDUCTORS (Part of Tl and T2).	C17 thru C20	19A116656P5G0	Ceramic disc: 5 pf ±0.25 pf, 500 VDCW, temp coef 0 PPM.
L2		(Part of T3 and T4).	C21	19A116655P22	Ceramic disc: 2700 pf ±10%, 1000 VDCW; sim to
L3	19B209420P1	Coil, RF: 0.10 µh ±5%, 0.08 ohms DC res max; sim to Jeffers 4416-lJ.	C22	19A116655P20	RMC Type JF Discap.  Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to
			thru C24		RMC Type JF Discap.
Q1	19A115329P1		C25	5491601P123	Phenolic: 1.5 pf ±5%, 500 VDCW.
Q2	19411532991	Silicon, NPN. Silicon, NPN.	C26	19A116655P20	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.
			C27		(Part of T1).
		RESISTORS	C28	1	(Part of T2),
Rl	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	C29	5491601P130	Phenolic: 3.3 pf ±5%, 500 VDCW.
R2	3R152P181J	Composition: 180 ohms ±5%, 1/4 w.	C30	19A116656P39J0	Ceramic disc: 39 pf ±5%, 500 VDCW, temp coef
R3	3R152P100K	Composition: 10 ohms ±10%, 1/4 w.			O PPM.
R4	3R152P471K	Composition: 470 ohms ±10%, 1/4 w.	C31	5490008P135	Silver mica: 220 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
R5 R6	3R152P680J 3R152P273K	Composition: 68 ohms ±5%, 1/4 w.	C32	5490008P35	Silver mica: 220 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.
R7	3R152P100K	Composition: 27,000 ohms ±10%, 1/4 w.  Composition: 10 ohms ±10%, 1/4 w.	С33	19A116656P100J3	Ceramic disc: 100 pf ±5%, 500 VDCW, temp coef
			C34	19A116656P150J1	Ceramic disc: 150 pf ±5%, 500 VDCW, temp coef -150 PPM.
Tl and T2		COIL ASSEMBLY T1 198219098G1 T2 198219098C2	C35	5491601P123	Phenolic: 1.5 pf ±5%, 500 VDCW.
		T2 19B219098G2			DIODES AND RECTIFIERS
			CR1	19A115348P1	Silicon.
C2	5496218P346	Ceramic disc: 20 pf ±5%, 500 VDCW, temp coef -150 PPM.	thru CR4	-5/110010F1	,
сз	5496218P245	Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM.	CR5	19A115250P1	Silicon.
					•
		i	1	I	İ

SYMBOL	GE PART NO.	DESCRIPTION	SYMB	
		JACKS AND RECEPTACLES		
J1	4033513P4	Contact, electrical: sim to Bead Chain L93-3.	C2	
thru J8			СЗ	
Ll	7488079P16	Chaha Dr. 10 to 100	C4	
and L2	1400019910	Choke, RF: 10 µh ±10% ind at 640 ma, 0.6 ohm DC res; sim to Jeffers 4421-7K.	C5	
L3		(Part of Tl and T2).	and C6	
		TRANSISTORS	Q1	
Q1 and Q2	19A115330P1	Silicon, NPN.		
		RESISTORS	R1	
Rl thru	3R152P562J	Composition: 5600 ohms ±5%, 1/4 w.	R2	
R4 R5	3R152P104K	Composition: 0.1 megohm ±10%, 1/4 w.	R3	
thru R8	0#102F104#	Composition: U.1 megonm ±10%, 1/4 w.	R5	
R9	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.	R6	
R10	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.	R7	
R11 and R12	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.		
R13	3R152P151J	Composition: 150 ohms ±5%, 1/4 w.	T1	
R14	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.	A422	
R15	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.		
R17 and R18	3R152P103K	Composition: 10,000 ohms ±10%, 1/4 w.	FL7	
R20	3R152P270K	Composition: 27 ohms ±10%, 1/4 w.		
			R10	
RT1 thru	19B209284P7	Disc: 62 ohms res nominal at 25°C, color code violet.	R11	
RT5		TRANSFORMERS	A424	
Tl and		COIL ASSEMBLY		
T2		T1 19B219102G1 T2 19B219102G2	C2	
			сз	
C27	5496218P249	Ceramic disc: 27 pf ±5%, 500 VDCW, temp coef -80 PPM.	C7	
C28	5496218P248	Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef -80 PPM.	C8	
			1	
ŗ13	19A121728P1	Coil. Includes tuning slug 5491798P5.	C10 C12	
	5491798P7	Tuning slug.		
		SOCKETS	C14	
XY1 thru XY4		Refer to Mechanical Parts (RC-2422).	C15	
***			C16	
		NOTE: When reordering give GE Part No. and	C17	
-		specify exact freq needed.  Crystal freq = Oper, Freq -12.4 MHz.		
		24	C19	
Yl thru	19B206576P7	Quartz: freq range 17925.001 to 20685.000 KHz, temp range -30°C to +85°C. (470-494 MHz)	C20	
¥4			C23	
A421		IF AMPLIFIER ASSEMBLY 198216356G1	C24 and C25	
l				
C1	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	J1	
1			1	
I		l	1	

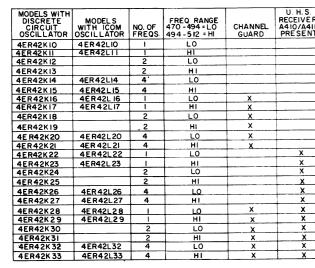
SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.
C2	7489162P21	Silver mica: 56 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.		
сз	5496218P650	Ceramic disc: 30 pf ±5%, 500 VDCW, temp	L1	19C311181G3
C4	5494481P11	coef -470 PPM.  Ceramic disc: 1000 pf ±20% 1000 VDCW sim to	L2 and L3	19A115711P1
C5	19A116080P5	RMC Type JF Discap. Polyester: 0.047 µf ±20%, 50 VDCW.		
and C6		100 pt 120%, 50 V20%.	P1 P2	4029840P2 4029840P1
		TRANSISTORS		4029840P1
Q1	19A115440P1	Silicon, NPN.		
		RESISTORS	Q2 Q3	19A115245P1 19A115123P1
R1	3R152P301J	Composition: 300 ohms ±5%, 1/4 w.	Q4	19A115245P1
R2	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.		
R3	3R152P152J	Composition: 1500 ohms ±5%, 1/4 w.		
R4	3R152P682J	Composition: 6800 ohms ±5%, 1/4 w.	R1 and R2	3R77P103K
R6	3R152P101K 3R152P301J	Composition: 100 ohms ±10%, 1/4 w.	R3	3R77P512J
R7	3R152P511J	Composition: 300 ohms ±5%, 1/4 w.	R4	3R152P333K
	08102F3113	Composition: 510 ohms ±5%, 1/4 w.	R5	3R152P103J
	:	TRANSFORMERS	R6	3R77P332K
Tl	19B216372G1	Coil assembly. Includes tuning slug 5491798P7.	R7	3R77P123K
A422		CRYSTAL FILTER ASSEMBLY	R8	3R77P622J
		19B204616G8	R9	3R77P302J
			R10	3R77P202J
FL7	19C304358G1	Bandpass filter.	Rll	3R77P201J
		RESISTORS		
R10	3R152P512J	Composition: 5100 ohms ±5%, 1/4 w.	Т2	
R11	3R152P332K	Composition: 3300 ohms ±10%, 1/4 w.		
A424		SECOND MIXER ASSEMBLY 19B216119G3	C23	5496218P258
		CAPACITORS		5491798P3
C2	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW.	1	
сз	5494481P112	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	Y2	19A110398P1
C7 and C8	19A116080P5	Polyester: 0.047 μf ±20%, 50 VDCW.	A426	
С9	5496219P369	Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef -150 PPM.		
C10	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW.	C1	5494481P111
C12	5496219P369	Ceramic disc: 180 pf ±5%, 500 VDCW, temp coef -150 PPM.	C2	5496219P717
C14	5496219P471	Ceramic disc: 220 pf ±5%, 500 VDCW, temp coef -220 PPM.	C3	5494481P111
C15	7491395P109	Ceramic disc: 1000 pf ±10%, 500 VDCW; sim to RMC Type JL.	C4	5496219P717
C16	19A116080P5	Polyester: 0.047 µf ±20%, 50 VDCW.		
C17	19A116080P1	Polyester: 0.01 µf ±20%, 50 VDCW.	C5 and C6	5494481P111
C18	5490008P25	Silver mica: 82 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	C6 €7-	19A116080P5
C19	5490008P19	Silver mica: 47 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	C8	19A116656P180J1
C20	5490008P1	Silver mica: 5 pf ±0.5%, 500 VDCW; sim to Electro Motive Type DM-15.	C9	5490008P37
C23		(Part of T2).	and C10	
C24	5496219P43	Ceramic disc: 13 pf ±5%, 500 VDCW, temp coef	C11	5496219P656
and C25		0 PPM.	C12	5494481P108
J1	4033513P4	JACKS AND RECEPTACLES Contact, electrical; sim to Bead Chain L93-3.	C12	3494481P108

	<b>-</b>	
DESCRIPTION	SYMBOL	GE PART NO.
INDUCTORS	C13	19All5680Pl07
rmer, freq: 455 KHz; sim to Automatic 2670.	C14 and C15	19A115680P104
PLUGS	C16	5494481P112
, electrical: sim to Amp 42827-2.	C17	19A116080P7
, electrical: sim to Amp 41854.	C18	5494481P108
TRANSISTORS	C19 and C20	19A116080P5
, NPN; sim to Type 2N2712.	C21	19A116080P3
, NPN.	C22	19A116080P108
RESISTORS	C23	19A116080P107
tion: 10,000 ohms ±10%, 1/2 w.	C25	5496267P6
	C26	19A116080P109
tion: 5100 ohms ±5%, 1/2 w.	C27	5496267P2
tion: 33,000 ohms ±10%, 1/4 w.	C30	19A116080P8
tion: 10,000 ohms ±5%, 1/4 w.	C31	19A116080P102
tion: 3300 ohms ±10%, 1/2 w. tion: 12,000 ohms ±10%, 1/2 w.	C32	19A116080P7
tion: 6200 ohms ±5%, 1/2 w.	C33	19A116080P9
tion: 3000 ohms ±5%, 1/2 w.	C34	4029003P207
tion: 2000 ohms ±5%, 1/2 w.	C35	19A116080P5
zion: 200 ohms ±5%, 1/2 w.	C36	19A116080P9
TRANSFORMERS	C37	5496267P28
COIL ASSEMBLY	C39	19A116080P1
19B216120G2	C40	5496267P28
CAPACITORS	C41	5490008P129
disc: 62 pf ±5%, 500 VDCW, temp PPM.		_
slug.	C50	19A116080P7
CRYSTALS	C51	19A116655P22
freq 11945.00 KHz, temp range -30°C	C52	19A116080P109
IF AUDIO AND SQUELCH BOARD	C53 and C54	5496267P213
19D413129G3	C55	5496267P14
CAPACITORS		
disc: 1000 pf ±20%, 1000 VDCW; sim to	CR1	19A115250P1
disc: 47 pf ±10%, 500 VDCW, temp coef	thru CR6	
disc: 1000 pf ±20%, 1000 VDCW; sim to JF Discap.	J1 thru	4033513P4
disc: 47 pf ±10%, 500 VDCW, temp coef	J22	
disc: 1000 pf $\pm 20\%$ , 1000 VDCW; sim to JF Discap.	L1	19Al15711P6
r: 0.047 µf ±20%, 50 VDCW.	L2	19A115711P7
disc: 180 pf ±5%, 500 VDCW, temp coef	L3	19A127134G1
ica: 270 pf ±5%, 500 VDCW; sim to Motive Type DM-15.	Q1 thru	19A115123P1
disc: 51 pf $\pm 5\%$ , 500 VDCW, temp coef.	Q6 Q7	19A115300P4
disc: 470 pf ±10%, 1000 VDCW; sim to JF Discap.	Q8	19A115123P1
	Q9	19A115362P1

Ī			<del>,</del>	
	Electrolytic: 100 µf +150% -10%, 15 VDCW; sim	Q10	19A116774P1	Silicon, NPN; sim to Type 2N5210.
ı	to Mallory Type TT.  Electrolytic: 50 µf +150% -10%, 25 VDCW; sim			
	to Mallory Type TT.	R1	3R77P102K	Composition: 1000 ohms ±10%, 1/2 w.
	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to	R2	3R77P153J	Composition: 15,000 ohms ±5%, 1/2 w.
	RMC Type JF Discap.	R3	3R77P823K	Composition: 82,000 ohms ±10%, 1/2 w.
	Polyester: 0.1 µf ±20%, 50 VDCW.	R4	3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.
	Ceramic disc: 470 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	R5	3R77P102K	Composition: 1000 ohms ±10%, 1/2 w.
	Polyester: 0.047 µf ±20%, 50 VDCW.	R6	3R77P153J	Composition: 15,000 ohms ±5%, 1/2 w.
		R7	3R77P823K	Composition: 82,000 ohms ±10%, 1/2 w.
	Polyester: 0.022 µf ±20%, 50 VDCW.	R8	3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.
	Polyester: 0.15 µf ±10%, 50 VDCW.	R9	3R77P102K	Composition: 1000 ohms ±10%, 1/2 w.
1	Polyester: 0.1 µf ±10%, 50 VDCW.	R10	3R77P153J	Composition: 15,000 ohms ±5%, 1/2 w.
	Tantalum: 33 μf ±20%, 10 VDCW; sim to Sprague	R11	3R77P823K	Composition: 82,000 ohms ±10%, 1/2 w.
	Type 150D.	R12	3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.
	Polyester: 0.22 µf ±10%, 50 VDCW.	R13	3R77P272K	Composition: 2700 ohms ±10%, 1/2 w.
	Fantalum: 47 μf ±20%, 6 VDCW; sim to Sprague Type 150D.	R14	3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.
1	Polyester: 0.15 µf ±20%, 50 VDCW.	R15	3R77P333J	Composition: 33,000 ohms ±5%, 1/2 w.
1	Polyester: 0.015 µf ±10%, 50 VDCW.	R16	3R77P181K	Composition: 180 ohms ±10%, 1/2 w.
1	Polyester: 0.1 µf ±20%, 50 VDCW.	R17	3R152P471J	Composition: 470 ohms $\pm 5\%$ , $1/4$ w.
I	Polyester: 0.22 µf ±20%, 50 VDCW.	R18	3R152P513J	Composition: 51,000 ohms ±5%, 1/4 w.
	Silver mica: 1830 pf ±2%, 500 VDCW; sim to Electro Motive Type DM-20.	R19		1
	Polyester: 0.047 µf ±20%, 50 VDCW.	R20	3R152P472K	Composition: 4700 ohms ±10%, 1/4 w.
	Polyester: 0.22 µf ±20%, 50 VDCW.	R21 and	3R77P362J	Composition: 3600 ohms ±5%, 1/2 w.
	Cantalum: 0.47 \( \mu f \) ±20%, 35 VDCW; sim to	R22		
	prague Type 150D.	R23	3R77P104K	Composition: 0.10 megohm ±10%, 1/2 w.
	Polyester: 0.01 μf ±20%, 50 VDCW.	R24	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.
	antalum: 0.47 $\mu$ f $\pm 20\%$ , 35 VDCW; sim to prague Type 150D.	R25 and R26	3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.
S	ilver mica: 120 pf ±10%, 500 VDCW; sim to lectro Motive Type DM-15.	R27 and	3R77P753J	Composition: 75,000 ohms ±5%, 1/2 w.
	olyester: 0.1 µf ±20%, 50 VDCW.	R28		
E	eramic disc: 2700 pf ±10%, 1000 VDCW; sim to MC Type JF Discap.	R29	3R77P182J	Composition: 1800 ohms ±5%, 1/2 w.
	olyester: 0.22 µf ±10%, 50 VDCW.	R30 and	3R77P821J	Composition: 820 ohms ±5%, 1/2 w.
	antalum: 2.2 μf ±10%, 20 VDCW; sim to Sprague	R31 R33	207700101	
	ype 150D.	R34	3R77P912J 3R77P332K	Composition: 9100 ohms ±5%, 1/2 w.
	antalum: 15 µf ±20%, 20 VDCW; sim to prague Type 150D.	R35	3R77P332K	Composition: 3300 ohms ±10%, 1/2 w.
•	prague Type 130D.	R36	3R77P681J	Composition: 33 hms ±10%, 1/2 w.
	DIODES AND RECTIFIERS	R38	3R77P752J	Composition: 680 ohms ±5%, 1/2 w.
	ilicon.	R39	3R77P820J	Composition: 7500 ohms ±5%, 1/2 w.  Composition: 82 ohms ±5%, 1/2 w.
		R40	3R77P241J	Composition: 240 ohms ±5%, 1/2 w.
	JACKS AND RECEPTACLES	R41	3R152P240J	Composition: 24 ohms ±5%, 1/4 w.
	ontact, electrical; sim to Bead Chain L93-3.	R42	3R77P200J	Composition: 20 ohms ±5%, 1/2 w.
		R43	19B209358P101	Variable, carbon film: approx 25 to 250 oh
	INDUCTORS	]		±10%, 0.2 w; sim to CTS Type X-201.
•	ransformer, freq: 455 KHz; sim to TOKO PEFCN- 4733-CX12.	R44	19B209022P101	Wirewound: 0.27 ohms $\pm 10\%$ , 2 w; sim to IRC Type BWH.
4	ansformer, freq: 455 KHz; sim to TOKO PEFCN-	R45	3R77P123J	Composition: 12,000 ohms ±5%, 1/2 w.
h	oke.	R46	3R77P913J	Composition: 91,000 ohms ±5%, 1/2 w.
	TRANSISTORS	R48	19A116278P249	Metal film: 3160 ohms ±2%, 1/2 w.
	ilicon, NPN; sim to Type 2N2712.	R49	3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.
		R50	3R77P222J	Composition: 2200 ohms ±5%, 1/2 w.
;	ilicon, NPN; sim to Type 2N3053.	R51	3R77P103J	Composition: 10,000 ohms ±5%, 1/2 w.
	ilicon, NPN; sim to Type 2N2712.	R52	3R77P682J	Composition: 6800 ohms ±5%, 1/2 w.
	ilicon, NPN; sim to Type 2N2925.	R54	3R77P822J	Composition: 8200 ohms ±5%, 1/2 w.
•	** ***			1

\*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

11



IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART.

ALL RESISTORS ARE 1/2 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR NALUES IN OHMS UNLESS FOLLOWED BY K=1000 OHMS OR MEG=1,000,000 OHMS OR MEG=1,000,000 OHMS OR MEG=1,000,000 OHMS OR MEG NEGOTARADS (BUALES) OF MEROMICROFARADS UNLESS FOLLOWED BY UNE MICROFARADS, INDUCTANCE VALUES IN MICROFIENRYS UNLESS FOLLOWED BY MH= MILLIHENRYS OR H= HENRYS.

VOLTAGE READINGS VOLTAGE READINGS ARE TYPICAL READINGS MEASURED TO SYSTEM NEGATIVE (J442-8) WITH TEST SET MODEL 4EX3AIO OR A 20,000 OHM-PER- VOLT METER.

S=NO SIGNAL IN WITH SQUELCH CONTROL FULLY
COUNTERCLOCKWISE (MAXIUM SQUELCH)
US=SQUELCH CONTROL FULLY CLOCKWISE WITH A ONE MILLIVOLT MODULATED SIGNAL (UNSQUELCHED) AND 5 WATT AUDIO OUTPUT.

TO CHECK FOR PROPER OPERATION OF IST MIXER A412, MEASURE CURRENT IOV CIRCUIT (W-R LEAD), CURRENT WITH FIRST OSC XTAL REMOVED SHOULD BE 0.6 TO 0.8 MA.
CURRENT WITH FIRST OSC OPERATING
PROPERLY, SHOULD BE 1.2 TO 1.6 MA.

■THESE ARE ONLY PARTS PRESENT ON A429. ●LOW SPLIT 470-494 MHZ

▲HIGH SPLIT 494-512 MHZ \*LEADS TO BE TERMINATED AS SHORT AS POSSIBLE.

VALUE OF A428-R47 IS DETERMINED BY TEST (SEE TEST SPEC 19A127182)

PLI9E500928G1
PLI9E500928G2
PLI9E500928G3
PLI9E500928G4
A424 PLI9B216119G3
A426 PLI9D413129G3 C
A428 4EKI6AIO A
A429 PLI9C311797G2

A417 PLI9C317606G3 A418 PLI9C317606G4 A420 PL19C317606G6

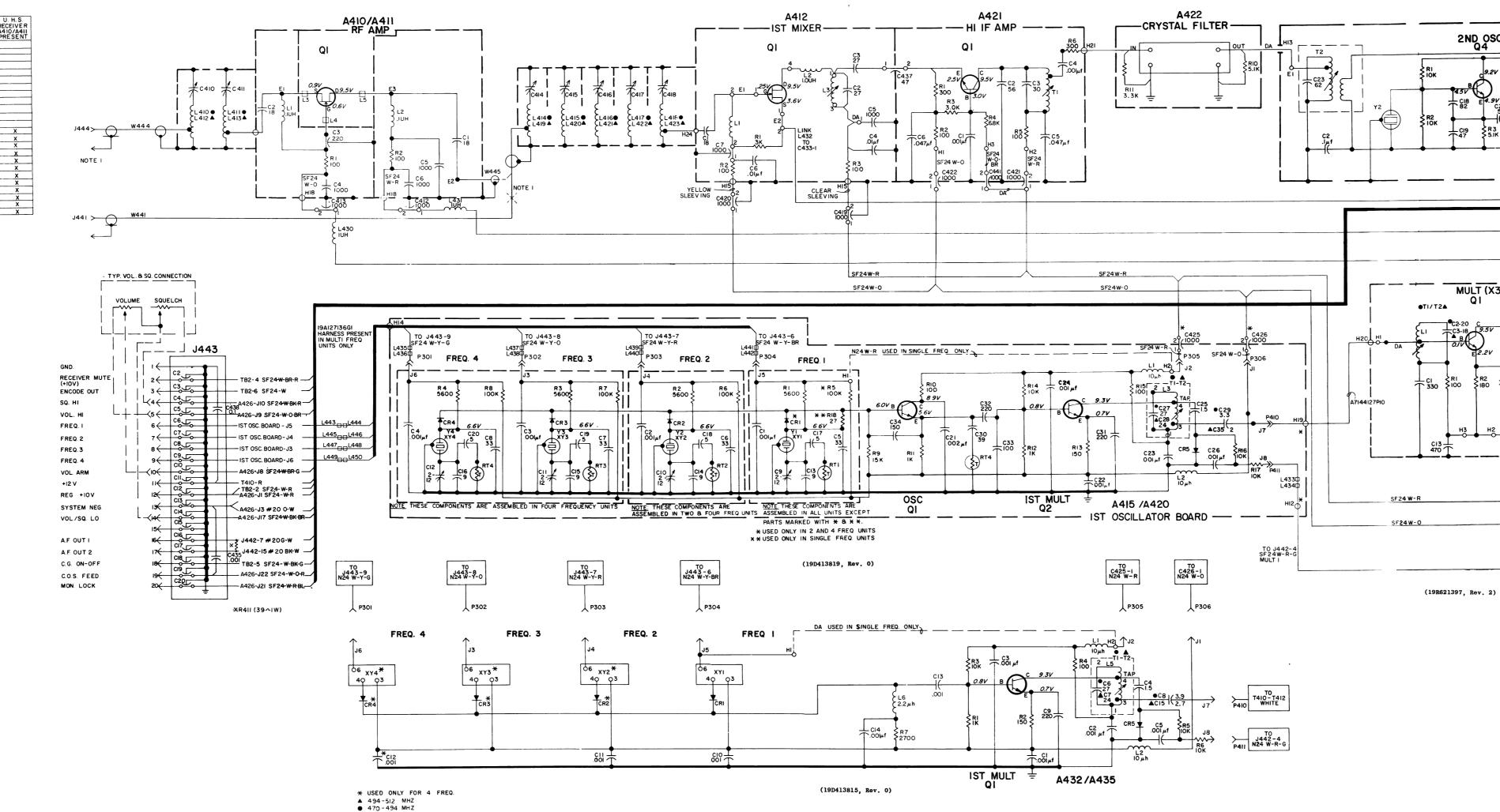
SYM NO. PARTS LIST LETTER
A432 PLI9C317654 GI
A433 PLI9C317654 G2
A434 PLI9C317654G3
A435 PLI9C317654G4

# SCHEMATIC DIAGRAM

470-512 MHz RECEIVER MODELS 4ER42K10-33 & 4ER42L10-33

1. W444 AND W445 PRESENT ONLY IN UHF RECEIVERS W441 PRESENT ONLY IN NON VHF RECEIVERS.

Issue :



A 424 ----- 2ND MIXER BOARD ------

MULT (X2)

SF24W-BK-BL

TO J442-1 SF24W-BK-BL MULT 2

•A413/A414▲

WRAP 8 SLV

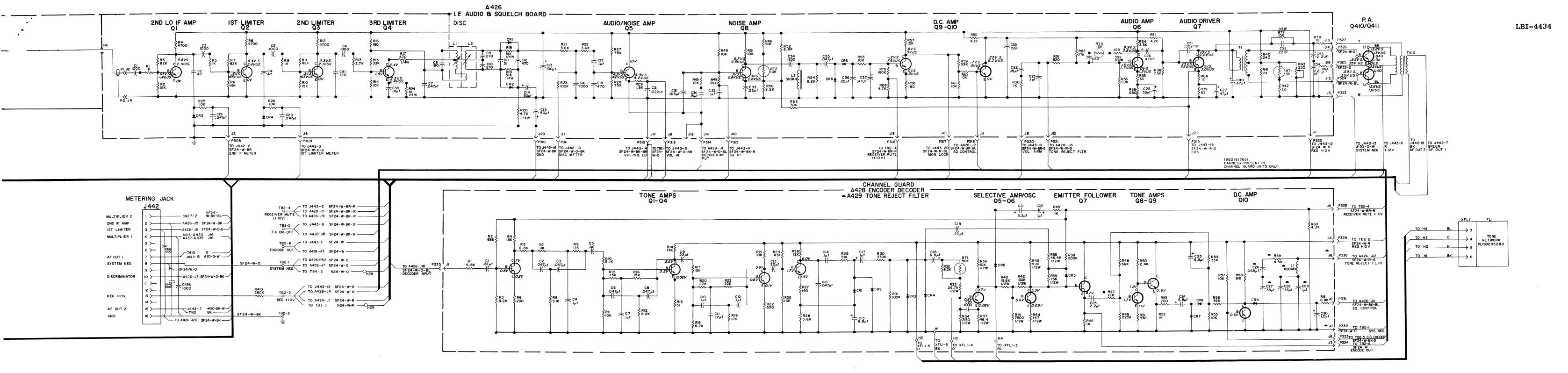
Q3

-⊥ C429 ↑ 50µf

TB4-MOUNTING

SF24W-R

TO TB2-2 SF24-W-R REG + IOV



(19R621397, Rev. 2)

# **SCHEMATIC DIAGRAM**

470—512 MHZ RECEIVER MODELS 4ER42K10-33 & 4ER42L10-33

SYMBOL GE PART NO.	DESCRIPTION	SYMBOL GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	. GE PART NO	. DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION	SYMBO	L GE PART NO.	DESCRIPTION	SYMBOL GE PART I	IO. DESCRIPTION
									SOCKETS	R3	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.	C441	5493392P7	Ceramic, feed-thru: 1000 pf +100%-0%, 500 VDCW; sim to Allen-Bradley Type FASC.			RESISTORS	23 4029851P6	Clip, loop,
R55 3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.	C23 5496267P13	Tantalum: 2.2 µf ±20%, 20 VDCW; sim to Sprague Type 150D.	1	3R152P301J 3R152P223J	Composition: 300 ohms ±5%, 1/4 w.	XFL1	19A121920G3	Reed, mica-filled phen: 7 pins rated at 1 amp	R4	3R152P101K	Composition: 100 ohms ±10%, 1/4 w.				R410	19A116278P444	Metal film: 0.28 megohm ±2%, 1/2 w.	24 19B204583G1	Hinge.
R57 3R77P103K R58 3R77P181K	Composition: 10,000 ohms ±10%, 1/2 w.  Composition: 180 ohms ±10%, 1/2 w.	C24 5496267P1	Tantalum: 6.8 µf ±20%, 6 VDCW; sim to Sprague Type 150D.		3R152P223J 3R152P433J	Composition: 22,000 ohms ±5%, 1/4 w.  Composition: 43,000 ohms ±5%, 1/4 w.			at 500 VRMS with 4-1/2 inches of cable.	R5	3R152P103K	Composition: 10,000 ohms ±10%, 1/4 w.	11		DIODES AND RECTIFIERS	R411	3R78P390K	Composition: 39 ohms $\pm 10\%$ , 1 w.	25 N115P1508C1	Screw, flathead, self tap: No. 8 x 30.
R59 3R77P393K	Composition: 39,000 ohms ±10%, 1/2 w.	C25 5496267P18	Tantalum: 6.8 µf ±20%, 35 VDCW; sim to	1 1	3R152P133J	Composition: 13,000 ohms ±5%, 1/4 w.	A429		TONE REJECT FILTER 19C311797G2	and R6			CR1	19A116062P2	Selenium.				26 19B204583G2	Hinge.
R60 3R77P103K	Composition: 10,000 ohms ±10%, 1/2 w.		Sprague Type 150D.	1 1	3R152P123J	Composition: 12,000 ohms ±5%, 1/4 w.	1		19631179702	R7	3R77P272K	Composition: 2700 ohms ±10%, 1/2 w.	11		JACKS AND RECEPTACLES	T410	19Al16041P2		27 19A121676P1	Guide pin.
and R61	1	C26 19A116080P206	Polyester: 0.068 μf ±5%, 50 VDCW.	1 1	3R152P151J	Composition: 150 ohms ±5%, 1/4 w,	-	1	CAPACITORS	l I		TRANSFORMERS	J441		(Part of W441).			Audio freq: freq range 300 to 4000 Hz, Pri: 1.00 ohm ±15% DC res, Sec 1: 0.23 ohm ±10% DC res,	28 19C303495G3	Top cover. (Station, except Repeaters and VM).
R64 3R77P120J	Composition: 12 ohms ±5%, 1/2 w.	C27 19A116080P210 and	Polyester: 0.33 µf ±5%, 50 VDCW.	R28	3R152P562J	Composition: 5600 ohms ±5%, 1/4 w.	1	1	, , , ,			COIL ASSEMBLY	J442	19B205689G2	Connector: 18 contacts rated at 5 amps min at 1000 VDC max.			Sec 2: 10.5 ohms ±15% DC res.	19C303676G2	Top cover. (Station, Repeater and VM only).
R66 3R77P472K	Composition: 4700 ohms ±10%, 1/2 w.	C28 C29 19A116080P205	Polyester: 0.047 µf ±5%, 50 VDCW.	R29	3R152P513J	Composition: 51,000 ohms ±5%, 1/4 w.	C27 and	19A116080P210	Polyester: 0.33 µf ±5%, 50 VDCW.	and T2		T1 19B219145G1 T2 19B219145G2	J443	19C303426G1	Connector: 20 pin contacts.			TERMINAL BOARDS	19C303385G2	Top cover. (Mobile).
R70 3R77P184J	Composition: 0.18 megohm ±5%, 1/2 w.	C30 5496267P17	Tantalum: 1.0 µf ±20%, 35 VDCW; sim to	R30 :	3R152P334J	Composition: 0.33 megohm ±5%, 1/4 w.	C28		1				J444		(Part of W444).	TBl	7487424P2	Miniature, phen: 1 terminal.	29 19A129106G1	Plate. (Located over RF Circuit).
R77 3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.	0430207717	Sprague Type 150D.	R31	3R152P104J	Composition: 0.1 megohm ±5%, 1/4 w.	C29	19A116080P205	Polyester: 0.047 µf ±5%, 50 VDCW.		1					TB2	7487424P26	Miniature, phen: 6 terminals.	30 19B201074P20	Tap screw, Phillips Pozidriv: 4-40 x 5/16.
R78 3R77P200J	Composition: 20 ohms ±5%, 1/2 w.		DIODES AND RECTIFIERS	R32	3R152P822J	Composition: 8200 ohms ±5%, 1/4 w.	1		JACKS AND RECEPTACLES	C6.	5496218P249	Ceramic disc: 27 pf ±5%, 500 VDCW, temp coef -80 PPM.			INDUCTORS	TB3	7487424P24	Miniature, phen: 3 terminals.	31 19A121297P2	Angle,
R79 3R152P393J	Composition: 39,000 ohms ±5%, 1/4 w.	CR1 19A115250P1	Silicon.	R33	19A116278P342	Metal film: 26,700 ohms ±2%, 1/2 w.	J6	4033513P4	Contact, electrical; sim to Bead Chain L93-3.	C7	5496218P248	Ceramic disc: 24 pf ±5%, 500 VDCW, temp coef	L410	19B204938G23	Coil.	TB4			32 7160861P4 33 4036555P1	Nut, sheet spring. (Used to secure cover).
R80 3R152P432J	Composition: 4300 ohms ±5%, 1/4 w.	and CR2		R34	19A116278P233	Metal film: 2150 ohms ±2%, 1/2 w.	J7			1 1		-80 PPM.	L411	19B204938G24	Coil.			CABLES	33 4036555P1 34 4035267P2	Insulator, disc. (Used with Q7 on A426).
R81 3R152P472J	Composition: 4700 ohms ±5%, 1/4 w.	CR3 5494922P1	Silicon.	R35	19A116278P365	Metal film: 46,400 ohms ±2%, 1/2 w.			INDUCTORS	11		INDUCTORS	L412 L413	19B204938G29 19B204938G30	C611.	W441	19B205634G3	Coaxial cable: 50 ohm, approx 5 inches long. Includes (J441) 19B209122P3 connector.	403526792	Button, plug. (On A426).
R82 3R77P273J	Composition: 27,000 ohms ±5%, 1/2 w.	and CR4		R36	19A116278P301	Metal film: 10,000 ohms ±2%, 1/2 w.	L1	19A115690P1	Coil, RF: 880 mh ±5%, sim to Artted AC5672.	L5	19A121728P1	Coil.	L414	19B204938G30	Coll.	W444	1 1		<del> </del>	
R84 3R77P203J	Composition: 20,000 ohms ±5%, 1/2 w.	CR5 19A115250P1	Silicon.	1	19A116278P65	Metal film: 46.4 ohms $\pm 2\%$ , $1/2$ w.			RESISTORS		5491798P7	Tuning slug.	1415	198204938G25 198204936P12	Cost		1 1	Coaxial cable: 50 ohm, approx 7 inches long. Includes (J444) 19B209122P4 connector.		
		CR6 4036887P3	Silicon, Zener.	1 I	3R152P204J	Composition: 0.2 megohm ±5%, 1/4 w.	R59	3R152P182J	Composition: 1800 ohms ±5%, 1/4 w.			ICOMS	thru L417	190504930512	"""	W445	19A122550G1	RF: 50 ohm imp, approx 4 inches long.		
RT1 5490828P41	Thermistor: 30 ohms ±10%, color code black,	CR7 19A115250P1	Silicon.	1 1	19A116278P385	Metal film: 75,000 ohms ±2%, 1/2 w.						NOTE: When reordering specify ICOM Frequency.	L418	19B204938G27	Coil		1	MULTI-FREQUENCY MODIFICATION KIT	l l	2 3 4567,8 9,10
	white; sim to Globar Type Bl211H-4.	thru CR9		1	19A116278P329	Metal film: 19,000 ohms ±2%, 1/2 w.	A432 thru		OSCILLATOR/MULTIPLIER BOARD A432 19C317654G1			ICOM Freq = Operating Freq -12.4 MHz.	L419	19B204938G27	Coil		1	19A127096Gl and G2		
RT2 5490828P9	Thermistor: 10,000 ohms ±10%, color code yellow; sim to Globar Type 551H-8.		JACKS AND RECEPTACLES	1 " 1	19A116278P285	Metal film: 7500 ohms ±2%, 1/2 w.	thru A435	1	A433 19C317654G2 A434 19C317654G3	γ1	4EG26A10	Integrated Circuit Oscillator Module (ICOM).	L419	198204938G31	Coil		19A127136G1	Harness assembly.		
RT3 5490828P9	Thermistor: 10,000 ohms ±10%, color code	J1 4033513P4	Contact, electrical sim to Bead Chain L93-3.	1 1	19A116278P412	Metal film: 130,000 ohms ±2%, 1/2 w.			A435 19C317654G4	thru Y4		(1002).	thru L422	135201350710		P301	4029840P2	Contact, electrical; sim to Amp 42827-2.		
	yellow; sim to Globar Type 551H-8.	thru J8		1 1	19A116278P269	Metal film: 5110 ohms ±2%, 1/2 w.			CAPACITORS	11	19D413070P1	Cap, decorative.	L423	19B204938G26	Coil	P304	1 1	(Part of 19A127136Gl Harness assembly).		
	TRANSFORMERS		INDUCTORS	1 1	19A116278P117	Metal film: 147 ohms ±2%, 1/2 w.	c1	19A116655P20	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim	11			L424	19B204938G28	Coil	L435		Bead, ferrite. (Part of 19A127136G1 Harness	8	
Tl 19A116040P1	Audio freq: 300 to 4000 Hz,	L1 19A115690P1	Coil, RF: 880 mh ±5%, sim to Artted AC5672.	R45 and	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.	thru C3		to RMC Type JF Discap.			SOCKETS	L425	19B204936P12	Coil.	L442	1 1	assembly).		
	Pri: 19.3 ohms ±10% DC res, Sec: 23.5 ohms ±10% DC res.	1	TRANSISTORS	R46			C4	5491601P123	Phenolic: 1.5 pf ±5%, 500 VDCW; sim to Quality	XY1 thru	19B216043G1	Socket, (ICOM).	L426	19B204938G32	Coil.	L443	19A115700P2	Bead, ferrite.		@   @ T     @ ?
		Q1 19A115123P1	Silicon, NPN; sim to Type 2N2712.			The value of Resistor R47 must be obtained from			Components Type MC.	XY4			L427	19B204936P10	Coil.	L450	1		1      †	
A428	ENCODER/DECODER 4EK16A10	Q2 19A115362P1	Silicon, NPN; sim to Type 2N2925.			the component, then find corresponding value in parts list for the correct part number.	LS	19A116655P20	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	11		CHASSIS AND RF CIRCUIT	L428	7488079P18	Choke, RF: 15 µh ±10%, 1.2 ohms DC res; sim		1 1	MECHANICAL PARTS		
	CAPACITORS	Q3 19A115123P1	Silicon, NPN; sim to Type 2N2712.	R47A	3R152P822J	Composition: 8200 ohms ±5%, 1/4 w.	C6		(Part of T1).	11		19E500928G1 thru G4	and L429		to Jeffers 4421-9K.			(SEE RC-2422)	17	18 17 14 13 12 11
C1 19A116080P9	Polyester: 0.22 µf ±20%. 50 VDCW.	and 04	January States Type 20212.	R47B	3R152P912J	Composition: 9100 ohms ±5%, 1/4 w.	C7		(Part of T2).		İ	CAPACITORS	L430	7488079P6	Choke, RF: 1.0 µh ±10%, 0.30 ohms DC res; sim	1	19C303495G4	Bottom cover. (Station)	"A"	I6 I5
C2 19A116080P205	Polyester: 0.22 µ1 120%, 50 VDCW.	Q5 19A115362P1	Silicon, NPN; sim to Type 2N2925.	R47C	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.	C8	5491601P131	Phenolic: 3.9 pf ±5%, 500 VDCW.	C410		Refer to Mechanical Parts (RC-2422),	and L431		to Jeffers 4411-8K.		1	Bottom cover. (Mobile)		
and C3	Polyester. 0.047 µr ±5%, 50 Vicin.	thru Q8	,,,	R47D	3R152P113J	Composition: 11,000 ohms ±5%, 1/4 w.	C9	5490008P135	Silver mica: 220 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.	C411			L432	19A127433P1	Coil.	2	19C317344P3	Heat sink.		\ <u>L</u>
C4 19A116080P207	Polyester: 0.1 µf ±5%, 50 VDCW,	Q9 19A115123P1	Silicon, NPN; sim to Type 2N2712.	R47E	3R152P123J	Composition: 12,000 ohms ±5%, 1/4 w.	C10	19A116655P20	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim	C412 and	5493392P7	Ceramic, feed-thru: 1000 pf +100%-0%, 500 VDCW; sim to Allen-Bradley Type FA5C.	L433	19Al15700P2	Bead, ferrite.	3	19A121723P1	Support. (Mounts C425 and C426)		
C5 19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW.	and Q10		R47F	3R152P133J	Composition: 13,000 ohms ±5%, 1/4 w.	thru C14		to RMC Type JF Discap.	C413	1	Jam to Allen-Brauley Type FASC.	and L434			4	1	Clip. (Part of XY1-XY4).		
C6 19A116080P205	Polyester: 0.047 µf ±5%, 50 VDCW.	1	RESISTORS	R47G	3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.	C15	5491601P128	Phenolic: 2.7 pf ±5%, 500 VDCW.	C414 thru		Refer to Mechanical Parts (RC-2422).	11			5	1 1	Rivet. (Part of XY1-XY4).		VIEW "A"
C7 19A116080P207	Polyester: 0.1 µf ±5%, 50 VDCW.	R1 3R152P682K	Composition: 6800 ohms ±10%, 1/4 w.		3R152P752J	Composition: 7500 ohms ±5%, 1/4 w.				C418			P305	4029840P2	Contact, electrical: sim to Amp 42827-2.	6	19A115793P1	Contact. (Part of XY1-XY4).		-
C8 19A116080P205	Polyester: 0.047 µf ±5%, 50 VDCW.	R2 3R152P683J	Composition: 68,000 ohms ±5%, 1/4 w.	I   I	3R152P563J	Composition: 56,000 ohms ±5%, 1/4 w.			DIODES AND RECTIFIERS	C419 thru	5493392P7	Ceramic, feed-thru: 1000 pf +100%-0%, 500 VDCW; sim to Allen-Bradley Type FA5C.	thru P311			7	4039307P1	Crystal socket. (Part of XY1-XY4).	19 20 21 22	2,3 24 25 26 27
C9 19A116080P9	Polyester: 0.22 µf ±20%, 50 VDCW.	R3 3R152P822J	Composition: 8200 ohms ±5%, 1/4 w.	1 1	3R152P224J	Composition: 0.22 megohms ±5%, 1/4 w.	CR1 thru	19A115250P1	Silicon.	C422			P312	4029840P3	Contact, electrical: sim to Amp 42101-2.	8	19A122008P1	Insulator. (Part of XY1-XY4).		
C10 19A116080P207	Polyester: 0.1 µf ±5%, 50 VDCW.	R4 3R152P152J	Composition: 1500 ohms ±5%, 1/4 w.		3R152P242J	Composition: 2400 ohms ±5%, 1/4 w.	CR5			C423 and		Refer to Mechanical Parts (RC-2422).	P313	4029840P2	Contact, electrical: sim to Amp 42827-2.	9	4029387P4	Nut, sheet spring.	F	
C11 19A116080P109	Polyester: 0.22 µf ±10%, 50 VDCW.	R5 3R152P682K	Composition: 6800 ohms ±10%, 1/4 w.		3R152P331J	Composition: 330 ohms ±5%, 1/4 w.			JACKS AND RECEPTACLES	C424	1		P315	4029840P2	Contact, electrical: sim to Amp 42827-2.	10	19A115332P3	Tap screw: No. 6-32 x 5/16.		
C12 19A116080P207	Polyester: 0.1 µf ±5%, 50 VDCW.	R6 3R152P201J	Composition: 200 ohms ±5%, 1/4 w.		3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.	J1 thru	4033513P4	Contact, electrical: sim to Bead Chain L93-3.	C425 thru	5493392P7	Ceramic, feed-thru: 1000 pf +100%-0%, 500 VDCW; sim to Allen-Bradley Type FA5C.	P317			11	4035306P59	Fiber washer. (Used with Y2).		
C13 19A116080P9	Polyester: 0.22 µf ±20%, 50 VDCW.	R7 19A116278P305	Metal film: 11,000 ohms ±2%, 1/2 w.		3R152P201J	Composition: 200 ohms ±5%, 1/4 w.	18		INDICTIONS	C427	5.40¢00000		P319 and	4029840P2	Contact, electrical: sim to Amp 42827-2.	12	4034252P5	Can. (Used with Tl).		
C14 19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW.	R8 3R152P562J	Composition: 5600 ohms ±5%, 1/4 w.	1 1	3R152P333J	Composition: 33,000 ohms ±5%, 1/4 w.		7488079P16		C428	5496267P11	Tantalum: 68 µf ±20%, 15 VDCW; sim to Sprague Type 150D.	P320			13	19C303389G1	Chassis,		
C15 5496267P1	Tantalum: 6.8 µf ±20%, 6 VDCW; sim to	R9 19A116278P305	Metal film: 11,000 ohms ±2%, 1/2 w.	1 1	3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.	L1 and L2	1,4000,19510	Choke, RF: 10 µh ±10%, 0.6 ohm DC res max; sim to Jeffers 4421-7K.	C429	19A115680P4	Electrolytic: 50 µf +150% -10%, 25 VDCW; sim	P322	4029840P2	Contact, electrical: sim to Amp 42827-2.	14	19A121722P1	Plate.	111 /6	
C16 19A116080P5	Sprague Type 150D,	R10 3R152P512J	Composition: 5100 ohms ±5%, 1/4 w.		3R152P363J	Composition: 10 000 ohms ±5%, 1/4 w.	L2 L5		(Part of Tl and T2).	C430	5493392P7	to Mallory Type TT.	P323	4029840P1	Contact, electrical: sim to Amp 41854.	15	4036765G5	Screw. (Part of C410, C411, C414-C418, C423 and C424).		
C16 19A116080P5	Polyester: 0.047 µf ±20%, 50 VDCW.  Tantalum: 1.0 µf ±5%, 35 VDCW; sim to	R11 3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.	1   1	3R152P103K 3R152P913J	Composition: 10,000 ohms ±10%, 1/4 w.  Composition: 91,000 ohms ±5%, 1/4 w.	L6	7488079P35	Choke, RF: 2.20 µh ±10%, 0.50 ohms DC res max;	and C431	010303921	Ceramic, feed-thru: 1000 pf +100%-0%, 500 VDCW; sim to Allen-Bradley Type FA5C.	P324	4029840P2	Contact, electrical: sim to Amp 42827-2.	16	7137968P8	Nut, stamped: thd size No. 6-32; sim to Palnut		
51. 513020/P41/	Sprague Type 150D.	R12 3R152P822J	Composition: 8200 ohms ±5%, 1/4 w.		3R152P913J 3R152P182J	Composition: 91,000 ohms ±5%, 1/4 w.  Composition: 1800 ohms ±5%, 1/4 w.	"		sim to Jeffers 4412-9K.	C431	5493392P107	Ceramic stand-off: 1000 ms .1000 on soo	P325	4029840P1	Contact, electrical: sim to Amp 41854.		1 1	T0632005. (Part of C410, C411, C414-C418, C423 and C424).	3	4 33 32 31 30 29 28
C18 5496267P1	Tantalum: 6.8 µf ±20%, 6 VDCW; sim to Sprague Type 150D.	R13 3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.	I   I	3R152P182J	Composition: 4300 ohms ±5%, 1/4 w.			TRANSISTORS		0493392P107	Ceramic, stand-off: 1000 pf +100%-0%, 500 VDCW; sim to Allen-Bradley Type SS5D.	P326	4029840P2	Contact, electrical: sim to Amp 42827-2.	17	1	Support. (Mounts C419 and C420).		
C19 19A116080P109	1	R14 3R152P133J	Composition: 13,000 ohms ±5%, 1/4 w.	1 1	3R152P432J 3R152P682K	Composition: 4300 ohms ±10%, 1/4 w.	) o1	19A115991P1	Silicon, NPN.	C435	7774750P4	Ceramic disc: .001 µf +100% -0%, 500 VDCW.	P327	4029840P1	Contact, electrical: sim to Amp 41854.	18	1	Support. (Mounts C427, C430 and C431).		RC-2422
C20 5494481P111	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to	R15 3R152P510J	Composition: 51 ohms ±5%, 1/4 w.	, and	JAIOZI GOZK		"			C436			P410 and	4029840P1	Contact, electrical: sim to Amp 41854.	19	19B204583G3	Hinge.		
	RMC Type JF Discap.	R16 3R152P153J	Composition: 15,000 ohms ±5%, 1/4 w.						RESISTORS	C437	5493392P3	Ceramic, feed-thru: 47 pf +100% -0%, 500 VDCW; sim to Allen-Bradley Type FASC.	P411			20	1	Support. (Used with Q410 and Q411).		
C21 5496267P9	Tantalum: 3.3 µf ±20%, 15 VDCW; sim to Sprague Type 150D.	R17 3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.	RT1	5490828P22	Thermistor: 50,000 ohms ±10%, color code yellow; sim to Globar Type 763H.	11	3R152P102J	Composition: 1000 ohms ±5%, 1/4 w.	C438	19A116080P7	Polyester: 0.1 µf ±20%, 50 VDCW.		10411674171	TRANSISTORS	21	i 1	Plate, insulated. (Used with Q410 and Q411).		
C22 5496267P17	Tantalum: 1.0 µf ±20%, 35 VDCW; sim to	R18 3R152P622J	Composition: 6200 ohms ±5%, 1/4 w.				R2	3R152P151J	Composition: 150 ohms ±5%, 1/4 w.	C439	5494481P11	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to	and	19A116741P1	Silicon, NPN.	22	i i	Insulator. (Used with Q410 and Q411).		
	Sprague Type 150D.	R19 3R152P123J	Composition: 12,000 ohms ±5%, 1/4 w.		1		]			and C440		RMC Type JF Discap.	Q411				]			
	1	R20 3R152P223J	Composition: 22,000 ohms ±5%, 1/4 w.																	
		R21 3R152P103J	Composition: 10,000 ohms ±5%, 1/4 w.																	
											1							÷		
	1				1									1			1			
				l L l	1	L	J L			J	<u> </u>	<u> </u>		<del></del>	<u> </u>				I	

### ORDERING SERVICE PARTS

Each component appearing on the schematic diagram is identified by a symbol number, to simplify locating it in the parts list. Each component is listed by symbol number, followed by its description and GE Part Number.

Service parts may be obtained from Authorized GE Communication Equipment Service Stations or through any GE Radio Communication Equipment Sales Office. When ordering a part, be sure to give:

- GE Part Number for component

- Description of part
   Model number of equipment
   Revision letter stamped on unit

These instructions do not purport to cover all details or variations in equipment nor to provide for every possible contingency to be met in connection with installation, operation or maintenance.

Should further information be desired, or should particular problems arise which are not covered sufficiently for the purchaser's purposes, contact the nearest Radio Communication Equipment Sales Office of the General Electric Company.

# **MAINTENANCE MANUAL**

LBI-4434

MOBILE RADIO DEPARTMENT
GENERAL ELECTRIC COMPANY • LYNCHBURG, VIRGINIA 24502

